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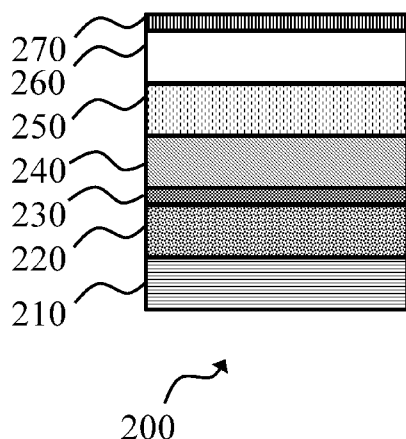
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(54) Title: NANOSTRUCTURE-CONTAINING ORGANIC-METAL HALIDE PEROVSKITES



(57) **Abstract:** Described herein is a device that includes an alkyl ammonium metal halide perovskite layer, and a nanostructured semiconductor layer in physical contact with the alkyl ammonium metal halide perovskite layer. The alkyl ammonium metal halide perovskite layer may include methyl ammonium cations. The alkyl ammonium metal halide perovskite layer may include anions of at least one of chlorine, bromine, astatine, and/or iodine. The alkyl ammonium metal halide perovskite layer may include cations of a metal in a 2+ valence state. The metal may include at least one of lead, tin, and/or germanium.

Figure 2

NANOSTRUCTURE-CONTAINING ORGANIC-METAL HALIDE PEROVSKITES

CONTRACTUAL ORIGIN

The United States Government has rights in this invention under Contract No. DE-AC36-08GO28308 between the United States Department of Energy and the Alliance for Sustainable Energy, LLC, the Manager and Operator of the National Renewable Energy Laboratory.

CROSS-REFERENCE TO RELATED APPLICATIONS

This application claims the benefits of U.S. Provisional Application No. 62/261,720 filed December 1, 2015, the contents of which are incorporated herein by reference in their entirety.

BACKGROUND

Metal-halide based perovskite solar cells have rapidly emerged as a promising alternative to traditional inorganic and thin-film photovoltaics. Metal-halide perovskite solar cells have demonstrated dramatic improvements in efficiencies over the past six years, rising from about 3% in 2009 to above 20% in 2015. These hybrid organic/inorganic photovoltaics embody many advantages of inexpensive solution-processed solar cells (e.g. bulk heterojunction organic photovoltaic (PV) devices, dye-sensitized cells, etc.), but at greater power conversion efficiencies that compare favorably with established inorganic technologies, such as CdTe and polycrystalline silicon. Despite the rapid rise in efficiency, a number of fundamental operational principles of perovskite solar cells are still poorly understood. Particularly important are the mechanisms and rates by which photogenerated charge carriers (1) recombine within neat perovskite films (either within the bulk or through traps), (2) diffuse to interfaces with electron and hole transport layers (ETL and HTL), (3) are transferred across these interfaces, and (4) recombine following extraction by the ETL and HTL. The rates for these competing processes help to determine the ultimate efficiency of devices. Rapid diffusion and interfacial charge transfer compete with recombination within the perovskite layer and aid in charge extraction by the ETL and HTL, enhancing photocurrent. Suppressing back-transfer from the ETL and HTL into the alkyl ammonium metal halide perovskite layer should result in long-lived charge separation and reduced recombination losses to the open circuit voltage and fill factor.

SUMMARY

An aspect of the present disclosure is a device that includes an alkyl ammonium metal halide perovskite layer, and a nanostructured semiconductor layer in physical contact with the alkyl ammonium metal halide perovskite layer. In some embodiments of the present disclosure, the alkyl ammonium metal halide perovskite layer may include methyl ammonium cations. In some embodiments of the present disclosure, the alkyl ammonium metal halide perovskite layer may include anions of at least one of chlorine, bromine, astatine, and/or iodine. In some embodiments of the present disclosure, the alkyl ammonium metal halide perovskite layer may include cations of a metal in a 2+ valence state. In some
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embodiments of the present disclosure, the metal may include at least one of lead, tin, and/or germanium.

In some embodiments of the present disclosure, the nanostructured semiconductor layer may include a plurality of an organic nanostructure. In some embodiments of the present disclosure, the organic nanostructure may include at least one of carbon nanotubes, graphene quantum dots, and/or carbon dots. In some embodiments of the present disclosure, the nanostructured semiconductor layer may include a plurality of an inorganic nanostructure. In some embodiments of the present disclosure, the inorganic nanostructure may include at a transition metal dichalcogenide. In some embodiments of the present disclosure, the inorganic nanostructure may include at least one of phosphine, silicone, and/or germanene.
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In some embodiments of the present disclosure, the inorganic nanostructure may include at least one of quantum dots, nanorods, nanowires, and/or nanosheets. In some embodiments of the present disclosure, the inorganic nanostructure may include at least one of CdS, CdSe, PbSe, InAs, InP, and/or InSb.

In some embodiments of the present disclosure, the device may further include a hole transport layer, where the nanostructured semiconductor layer may be positioned between the hole transport layer and the alkyl ammonium metal halide perovskite layer, and the nanostructured semiconductor layer may be in physical contact with the hole transport layer. In some embodiments of the present disclosure, the hole transport layer may include at least one of spiro-MeOTAD, polyhexyl (3-thiophene), and/or an inorganic oxide. In some
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embodiments of the present disclosure, the device may further include a conducting layer positioned above the hole transport layer. In some embodiments of the present disclosure, the device may further include an electron transport layer, where the alkyl ammonium metal

halide perovskite layer may be positioned between the hole transport layer and the electron transport layer. In some embodiments of the present disclosure, the device may further include a transparent conducting oxide layer positioned below the electron transport layer. In some embodiments of the present disclosure, the device may further include a substrate positioned below the transparent conducting oxide layer.

BRIEF DESCRIPTION OF THE DRAWINGS

Exemplary embodiments are illustrated in referenced figures of the drawings. It is intended that the embodiments and figures disclosed herein are to be considered illustrative rather than limiting.

Figure 1 illustrates alkyl ammonium metal halide perovskite crystal structure, according to some embodiments of the present disclosure.

Figure 2 illustrates a device that includes an alkyl ammonium metal halide perovskite layer in physical contact with a nanostructured semiconductor layer, according to some embodiments of the present disclosure.

Figure 3a illustrates a $\text{TiO}_2/\text{MAPbI}_3/\text{SWCNT}$ trilayer device with the excitation directions indicated for “backside” (BS) and “frontside” (FS) illumination, according to some embodiments of the present disclosure; MAPbI_3 (methyl ammonium lead iodide); SWCNT (single-walled carbon nanotubes).

Figure 3b illustrates optical absorption spectra (corrected for reflection in an integrating sphere) for $\text{TiO}_2/\text{MAPbI}_3$ and $\text{TiO}_2/\text{MAPbI}_3/(6,5)$ samples, along with a neat 9 nm (6,5) SWCNT film for comparison, according to some embodiments of the present disclosure. The first and second excitonic transition of the s-SWCNTs (S_{11} and S_{22}) are labeled. The offset spectrum is the differential absorption spectrum for a chemically doped (p-type) (6,5) SWCNT film.

Figures 3c and 3e illustrate TA spectra for a $\text{TiO}_2/\text{MAPbI}_3$ bilayer at various temporal delays, according to some embodiments of the present disclosure.

Figures 3d and 3f illustrate TA spectra for $\text{TiO}_2/\text{MAPbI}_3/(6,5)$ trilayer at various pump-probe delays, according to some embodiments of the present disclosure.

Figure 4a illustrates transient absorption dynamics of s-SWCNT hole extraction, specifically MAPI bleach recovery dynamics, measured at 750 nm for five different samples,

according to some embodiments of the present disclosure. The excitation wavelength was 400 nm, backside illumination.

Figure 4b illustrates a comparison of the TA spectrum of a $\text{TiO}_2/\text{MAPI}/(6,5)$ trilayer at a delay of 3.8 ns to the differential spectrum of a chemically doped (6,5) film, according to some embodiments of the present disclosure. The excitation wavelength was 400 nm, backside illumination.

Figure 4c illustrates an inverted, corrected and rescaled transient of S_{11} exciton bleach (1000 nm) for a $\text{TiO}_2/\text{MAPbI}_3/(6,5)$ trilayer compared to a MAPbI_3 band edge bleach (750 nm), according to some embodiments of the present disclosure. The excitation wavelength was 400 nm, backside illumination.

Figure 4d illustrates long-delay dynamics of MAPI bleach recovery (750 nm) and (6,5) S_{11} bleach recovery (1000 nm) for a $\text{TiO}_2/\text{MAPI}/(6,5)$ trilayer, according to some embodiments of the present disclosure. The solid line shows an exponential fit to the S_{11} bleach recovery, with $\tau_1 = 40 \mu\text{s}$ and $\tau_2 = 416 \mu\text{s}$. The excitation wavelength was 400 nm, backside illumination.

Figure 5 illustrates a comparison of normalized kinetics at 750 nm for samples pumped at 400 nm over the first 500 ns, according to some embodiments of the present disclosure.

Figure 6 illustrates time-resolved PL (tr-PL) transients for a TiO_2/MAPI bilayer sample and a $\text{TiO}_2/\text{MAPI}/(6,5)\text{-SWCNT}$ trilayer sample, according to some embodiments of the present disclosure. The long time constant in the $\text{TiO}_2/\text{MAPbI}_3/\text{LV}$ sample may represent delayed fluorescence from the recombination process where carriers are slow transferred from the ETL and HTL back into the MAPbI_3 layer.

Figures 7a and 7b illustrate a comparison of kinetics at 750 nm for samples pumped at 700 nm (Figure 7a) and 500 nm (Figure 7b), according to some embodiments of the present disclosure. Samples with the (6,5) SWCNT HTL exhibit faster bleach recovery than those without the (6,5) HTL.

Figures 8a and 8b illustrate a summary of the interfacial band alignment obtained by photoelectron spectroscopy measurements for a $\text{MAPI}/(6,5)\text{-SWCNT}$ interface (Figure 8a), and a MAPI/spiro interface (Figure 8b), according to some embodiments of the present disclosure. Note the opposite direction of band bending for each HTL, and that the band

bending within the SWCNT HTL should provide an energetic barrier for back-transfer of holes to the MAPI valence band.

Figures 9a and 9b illustrate TRMC results for MAPbI₃ films with various electron and hole transport layers, according to some embodiments of the present disclosure. Figure 9a illustrates yield-mobility product as a function of incident photon fluence for four different samples. Figure 9b illustrates time-resolved microwave conductivity transients for the same four samples, normalized at the peak (end-of-pulse) intensity. Excitation wavelength was 430 nm, backside illumination.

Figures 10a and 10b illustrate a summary of important dynamic processes occurring within MAPI and at the interfaces with the SWCNT HTL and TiO₂ ETL, according to some embodiments of the present disclosure. Figure 10a illustrates a kinetic scheme and schematic for dynamic processes in photoexcited MAPI absorber layer with SWCNT HTL and TiO₂ ETL. Processes above the dashed line result in charge extraction, and below line result in recombination. Each process is color-coded. Figure 10b illustrates a schematic of the time scale of each process described in Figure 10a, as well as the measurement technique and probe wavelength used to extract the kinetic information for the processes.

Figures 11a-c illustrate solar cell performance with and without SWCNT interfacial layers, according to some embodiments of the present disclosure. Figure 11a illustrates a device schematic for a MAPI solar cell with a s-SWCNT interfacial layer between the MAPI absorber layer and the spiro-MeOTAD HTL. Figure 11b illustrates J-V curves for typical MAPI devices, with or without a 5 nm (6,5) s-SWCNT interfacial layer. Figure 11c illustrates the external quantum efficiency for the same two devices as in Figure 11b.

Figure 12 illustrates representative stability experiments for devices prepared with or without 5 nm (6,5) s-SWCNT interfacial layers, according to some embodiments of the present disclosure. Initial efficiencies for (6,5)-modified devices were 16.3% and 16.5%, and initial efficiencies for devices without (6,5) interfacial layers were 12.3% and 13.7%.

Figure 13 illustrates control pump-probe experiments showing TA spectra for neat (6,5) SWCNT thin film (10 nm) pumped at 400 nm with fluence of 2×10^{11} photons/cm²/pulse, according to some embodiments of the present disclosure. This fluence corresponds to the illumination intensity seen by the SWCNT HTL following Beer-Lambert decay through the MAPI layer upon “backside” illumination for trilayer samples measured in the main manuscript. The control experiment demonstrates that no signal can be seen for the

SWCNTs under these illumination conditions, confirming that all signal in the SWCNT layer for a trilayer (TiO₂/MAPI/SWCNT) sample results from hole transfer from the photoexcited MAPI layer into the SWCNT thin film.

Figures 14a and 14b illustrate representative TA spectra for a frontside illumination experiment on a TiO₂/MAPbI₃/(6,5) trilayer sample, according to some embodiments of the present disclosure.

Figure 15 illustrates modeling of the TA dynamics at 1000 nm (rise time of (6,5) s-SWCNT holes) and at 750 nm (loss of MAPI holes) for photoexcited trilayer sample (TiO₂/MAPI/(6,5)-SWCNT) following photoexcitation at 400 nm, according to some embodiments of the present disclosure.

REFERENCE NUMBERS

100.....	alkyl ammonium metal halide perovskite
110.....	cation
120.....	cation
130.....	anion
200.....	device
210.....	transparent substrate layer
220.....	transparent conducting oxide layer
230.....	electron transport layer
240.....	alkyl ammonium metal halide perovskite layer
250.....	nanostructured semiconductor layer
260.....	hole transport layer
270.....	conducting layer

DETAILED DESCRIPTION

The present disclosure may address one or more of the problems and deficiencies of the prior art discussed above. However, it is contemplated that some embodiments as disclosed herein may prove useful in addressing other problems and deficiencies in a number of technical areas. Therefore, the embodiments described herein should not necessarily be construed as limited to addressing any of the particular problems or deficiencies discussed herein.

The present disclosure demonstrates that highly enriched semiconducting single-walled carbon nanotube films enable rapid hole extraction from an alkyl ammonium metal halide perovskite layer (absorber layer) and extremely slow back-transfer and recombination. The energetically narrow and distinct spectroscopic signatures for charges within these carbon nanotube thin films enables the unambiguous temporal tracking of each charge carrier with time-resolved spectroscopies covering many orders of magnitude. It is also demonstrated that the use of thin interface layers of semiconducting single-walled carbon nanotubes between the alkyl ammonium metal halide perovskite layer and a prototypical hole transport layer significantly improves device efficiency and stability, and reduces hysteresis.

Despite their importance, the time scales for charge extraction by the ETL and HTL (as well as subsequent back-transfer and recombination) in perovskite solar cells are still poorly understood. An important contributing factor to this uncertainty is the lack of specific and narrow spectral signatures for charges in traditional ETL and HTL materials. For example, both TiO_2 and 2,2',7,7'-tetrakis-(N,N-di-p-methoxyphenyl-amine)-9,9'-spirobi-fluorene (spiro-MeOTAD), prototypical ETL and HTL materials, have broad featureless near-infrared (NIR) absorptions when charged with excess electrons or holes, respectively, and charge carriers within the alkyl ammonium metal halide perovskite layer itself also contribute to broad NIR absorption. These overlapping signals typically require complicated analyses for transient absorption (TA) measurements at a single wavelength (e.g. 1400 nm⁹), where carriers within all three layers of a device stack (ETL, alkyl ammonium metal halide perovskite layer, and HTL) may contribute some ill-defined amount to the observed transient signal. Thus, the present disclosure describes a technologically relevant experimental system that addresses these important challenges by utilizing a charge extraction layer (thin films of highly enriched semiconducting single-walled carbon nanotubes) with a well-defined and energetically narrow spectral signature in the charged state.

Highly enriched semiconducting SWCNTs (s-SWCNTs) can have important advantages for both fundamental interfacial charge transfer studies and improving efficiency in perovskite solar cells. First, the sharp optical transitions (spectral width ca. 30 meV) of species-pure s-SWCNTs can be used as sensitive spectroscopic signatures for charge transfer to or from s-SWCNTs. The narrow peak widths of these optical transitions solve the problem of broad absorption of charges in conventional charge extraction layers, and enable the tracking of charge extraction with *material specificity*. Additionally, ground-state charge transfer at the interface between methyl ammonium lead iodide (MAPbI_3) and s-SWCNTs

creates band bending in the s-SWCNT layer that should in principle hinder the back transfer of holes from the SWCNT HTL to the alkyl ammonium metal halide perovskite. Thus, the present disclosure utilizes s-SWCNT layers to serve two roles: (i) serve as a material-specific spectroscopic signature to track charge extraction and recombination within a MAPbI₃ device stack and (ii) enable very long-lived charge separation, enhancing the performance of MAPbI₃ solar cells.

The present disclosure summarizes studies examining electron and hole extraction from MAPbI₃ alkyl ammonium metal halide perovskite layers using time-resolved spectroscopy over time scales spanning femtoseconds to ca. 400 microseconds. The sharp excitonic transitions of a high-purity (6,5) s-SWCNT HTL enable the unambiguous deconvolution of the kinetic pathways for both electrons and holes. The results demonstrate that s-SWCNT HTLs can efficiently extract holes from an alkyl ammonium metal halide perovskite layer in sub-picosecond time scales, and that the resulting back-transfer of holes to MAPbI₃ occurs over hundreds of microseconds. The efficient charge extraction enabled by s-SWCNTs contrasts sharply with a spiro-MeOTAD HTL and a compact TiO₂ ETL, both of which are found to be relatively inefficient at extracting holes and electrons, respectively. The huge disparity (up to nine orders of magnitude) in the time scales for hole extraction and back-transfer to and from the s-SWCNTs suggest that s-SWCNT HTLs provide the efficient and long-lived charge separation needed for high-efficiency solar cells. This supposition is confirmed by the determination that an interfacial layer of s-SWCNTs, as thin as 5 nm in between the MAPbI₃ absorber layer and a spiro-MeOTAD HTL, improves the power conversion efficiency from ca. 14.2% to ca. 16.3%.

Figure 1 illustrates that alkyl ammonium metal halide perovskites may organize into cubic crystalline structures and described by the general formula ABX₃, where X is an anion and A and B are cations, typically of different sizes (A typically larger than B). In a cubic unit cell, the B-cation resides at the eight corners of a cube, while the A-cation is located at the center of the cube and is surrounded by 6 X-anions (located at the face centers) in an octahedral [MX₆]⁴⁻ cluster (unit structure). Typical inorganic perovskites include calcium titanium oxide (calcium titanate) minerals such as, for example, CaTiO₃ and SrTiO₃. In some embodiments of the present disclosure, the cation A may include a nitrogen-containing organic compound such as an alkyl ammonium compound. Cation B may include a metal and anion B may include a halogen.

Additional examples for cation A (110) include organic cations and/or inorganic cations. Organic cations of A (110) may be an alkyl ammonium cation, for example a C₁₋₂₀ alkyl ammonium cation, a C₁₋₆ alkyl ammonium cation, a C₂₋₆ alkyl ammonium cation, a C₁₋₅ alkyl ammonium cation, a C₁₋₄ alkyl ammonium cation, a C₁₋₃ alkyl ammonium cation, a C₁₋₂ alkyl ammonium cation, and/or a C₁ alkyl ammonium cation. Further examples of organic cations of A (110) include methylammonium (CH₃NH³⁺), ethylammonium (CH₃CH₂NH³⁺), propylammonium (CH₃CH₂CH₂NH³⁺), butylammonium (CH₃CH₂CH₂CH₂NH³⁺), formamidine (NH₂CH=NH²⁺), and/or any other suitable nitrogen-containing organic compound. In other examples, a cation A (110) may include an alkylamine. Thus, a cation A (110) may include an organic component with one or more amine groups. For example, cation A (110) may be an alkyl diamine halide such as formamidine (CH(NH₂)₂).

Examples of metal cations 120 include, for example, lead, tin, germanium, and or any other 2+ valence state metal that can charge-balance the alkyl ammonium metal halide perovskite 100. Examples for the anion X (130) include halogens: e.g. fluorine, chlorine, bromine, iodine and/or astatine. In some cases, the alkyl ammonium metal halide perovskite may include more than one anion X (130), for example pairs of halogens; chlorine and iodine, bromine and iodine, and/or any other suitable pairing of halogens. In other cases, the alkyl ammonium metal halide perovskite 100 may include two or more halogens of fluorine, chlorine, bromine, iodine, and/or astatine.

Thus, cation A (110), cation B (120), and anion X (130) may be selected within the general formula of ABX₃ to produce a wide variety of alkyl ammonium metal halide perovskites 100, including, for example, methylammonium lead triiodide (CH₃NH₃PbI₃), and mixed halide perovskites such as CH₃NH₃PbI_{3-x}Cl_x and CH₃NH₃PbI_{3-x}Br_x. Thus, a alkyl ammonium metal halide perovskite 100 may have more than one halogen element, where the various halogen elements are present in none integer quantities; e.g. x is not equal to 1, 2, or 3. In addition, alkyl ammonium metal halide perovskites 100, like other organic-inorganic perovskites, can form three-dimensional (3-D), two-dimensional (2-D; e.g. sheets), one-dimensional (1-D; e.g. wires) or zero-dimensional (0-D; e.g. quantum dots) networks, possessing the same unit structure. In some embodiments of the present disclosure, the alkyl ammonium metal halide perovskite may be nanostructured.

As stated above, the anion A (110) may include an organic constituent in combination with a nitrogen constituent. In some cases, the organic constituent may be an alkyl group such as straight-chain or branched saturated hydrocarbon group having from 1 to 20 carbon

atoms. In some embodiments, an alkyl group may have from 1 to 6 carbon atoms. Examples of alkyl groups include methyl (C₁), ethyl (C₂), n-propyl (C₃), isopropyl (C₃), n-butyl (C₄), tert-butyl (C₄), sec-butyl (C₄), iso-butyl (C₄), n-pentyl (C₅), 3-pentanyl (C₅), amyl (C₅), neopentyl (C₅), 3-methyl-2-butanyl (C₅), tertiary amyl (C₅), and n-hexyl (C₆). Additional
5 examples of alkyl groups include n-heptyl (C₇), n-octyl (C₈) and the like.

Figure 2 illustrates a device 200, for example a photovoltaic device that includes a nanostructured semiconductor layer 250, for example the semiconductor form of single-walled carbon nanotubes (s-SWCNT). In other examples, the nanostructured semiconductor layer 250 may include a nanostructured transition metal dichalcogenide, M_xX₂, where M
10 includes Mo, W, Ti, V, Zr, and/or Hf and X includes S, Se, and/or Te. In further examples, the nanostructured semiconductor layer 250 may include phosphine (black phosphorous) and/or its variants, silicene, germanene, and/or semiconducting graphene (e.g. graphene quantum dots). In further examples, the nanostructured semiconductor layer 250 may include “carbon dots”, nanostructured carbon-based semiconductors. In yet further examples, the
15 nanostructured semiconductor layer 250 may include inorganic semiconductor nanostructures, such as nanocrystals (quantum dots), nanorods, nanowires, and/or nanosheets. Such inorganic semiconductor nanostructures may be constructed of CdS, CdSe, PbSe, InAs, InP, and/or InSb and/or any other suitable alloy and/or element. The nanostructured semiconductor layer 250 is positioned on, and in physical contact with, an alkyl ammonium
20 metal halide perovskite layer 240.

Figure 2 also illustrates other elements that may be included in a device 200. Starting from the bottom, and in order, a device 200 may include a transparent substrate layer 210 and a transparent conducting oxide layer 220 positioned on the transparent substrate layer 210. The transparent conducting oxide layer 220 may be, for example, a fluorine-doped tin oxide
25 layer. A device 200 may also include an electron transport layer (ETL) 230 positioned on the transparent conducting oxide layer 220, upon which may be positioned the alkyl ammonium metal halide perovskite layer 240 and then the nanostructured semiconductor layer 250. A device 200 may also include a hole transport layer (HTL) 260 positioned on the nanostructured semiconductor layer 250, and finally may include a conducting layer 270
30 positioned on hole transport layer 260. An example of an electron transport layer 230 includes titanium dioxide. An example of a hole transport layer 260 is a layer that includes spiro-MeOTAD. Other examples of materials for a hole transport layer 260 include

polyhexyl (3-thiophene), other semiconducting polymers, and/or inorganic oxides such as NiO and/or MoO₃. Examples of a conducting layer 270 include silver, gold, and/or copper.

Figure 3a illustrates a representative schematic of one of the primary trilayer stacks used for the time-resolved spectroscopic studies described herein – MAPbI₃ interfaced with both an ETL (compact TiO₂) and HTL (s-SWCNT). The HTL studies described herein focused primarily on near-monochiral (6,5) s-SWCNT thin films and lithium-doped spiro-MeOTAD. The (6,5) s-SWCNT HTL was enriched with > 99% semiconducting SWCNTs by a polyfluorene extraction procedure, and was constructed almost entirely of (6,5) s-SWCNTs (> 95%). Figure 3b displays absorbance spectra (corrected for reflectance) of three films studied herein. The solid trace shows MAPbI₃ deposited on a compact TiO₂ ETL (bilayer) and the dashed trace shows an identical bilayer stack capped with a 9 nm (6,5) s-SWCNT HTL (trilayer). The primary difference between the two spectra is the presence of a sharp transition at approximately 1000 nm, corresponding to the first excitonic transition (S₁₁) of the (6,5) s-SWCNTs (see lower dashed trace). The offset spectrum in Figure 3b shows a differential absorption spectrum ($\Delta A = A_{\text{doped}} - A_{\text{undoped}}$) for a (6,5) s-SWCNT film doped p-type with a well-characterized one-electron oxidant. The spectrum is dominated by two key peaks – a strong bleach of the S₁₁ exciton at 1000 nm and an induced absorption (IA) at 1170 nm, the latter having been assigned to the optical transition of a three-body trion quasiparticle. Importantly, the differential spectrum in Figure 3b demonstrates that two distinct spectral signatures may be used to follow hole extraction into the (6,5) s-SWCNT HTL.

Femtosecond TA spectra are shown in Figures 3c-f for a TiO₂/MAPbI₃ bilayer (Figures 3c/3e) and a TiO₂/MAPbI₃/(6,5) trilayer (Figures 3d/3f) with backside illumination (Figure 3a) at 400 nm. In the region of 550 – 800 nm, the bleach at 750 nm corresponds to a bleach of the MAPbI₃ band-edge excitonic transition. While the initial excited state was excitonic, the exciton rapidly (< 50 fs) decayed into uncorrelated charges due to the low exciton binding energy (ca. 9 – 16 meV). A broad induced absorption (IA) appeared between 850 – 1400 nm for both samples, and is related to charge carriers in MAPbI₃. However, the trilayer sample has a sharp bleach centered at approximately 1000 nm (asterisk, Figure 3f), corresponding to the (6,5) S₁₁ transition, superimposed on this broad IA. The (6,5) bleach was present at early times, prior to 1 ps delay, indicating very rapid hole transfer, and remained for the entire experimental window (approximately 5 ns).

Figure 4a shows the TA dynamics of several different samples probed at the MAPbI₃ band-edge bleach (750 nm). Since no HTL or ETL was present for the MAPbI₃/glass sample, the bleach recovery dynamics represent intrinsic electron-hole recombination dynamics within the neat perovskite (where “alkyl ammonium metal halide perovskite” is shortened to “perovskite”). Interestingly, the dynamics for TiO₂/MAPbI₃ and TiO₂/MAPbI₃/spiro were essentially identical to the MAPbI₃/glass sample, indicating that the bleach dynamics for both of the former samples are dominated by electron-hole recombination within the perovskite. The dynamics of the MAPbI₃ absorber layer on TiO₂ can be fit empirically with a biexponential decay with two characteristic time constants in the range of 8 ns and 50 ns (Figure 5, $\langle\tau\rangle = 42$ ns). The longer time constant is consistent with the photoluminescence (PL) lifetime ($\tau_{PL} = 60$ ns) extracted from time-resolved PL measurements (see Figure 6), which is attributed to monomolecular (Shockley-Read-Hall) non-radiative recombination.

In sharp contrast, the TiO₂/MAPbI₃/(6,5) sample showed much more rapid bleach recovery, indicating a new kinetic pathway where the s-SWCNT HTL removed charge carriers from the perovskite layer. The TA spectrum at a pump-probe delay of 3.8 ns is compared in Figure 4b to the chemically doped p-type (6,5) thin film. The two charge-related features, the s-SWCNT S₁₁ bleach at 1000 nm and the s-SWCNT trion at 1170 nm, provide unambiguous evidence for hole extraction from the perovskite layer into the adjacent s-SWCNT HTL. Figures 7a and 7b demonstrate that similar results were obtained for excitation at higher wavelength (e.g. 500 nm and 700 nm respectively). Additionally, Figure 4a shows that an HTL composed of laser vaporization (LV) s-SWCNTs, with significantly different band gaps, also efficiently extracted holes from the perovskite layer.

For the (6,5) trilayer sample, comparison of the rise time of the S₁₁ bleach (corrected for the superimposed MAPbI₃ IA and inverted) to the MAPbI₃ bleach recovery (see Figure 4c) demonstrates that both transients reflect the same kinetic process of hole extraction into the (6,5) SWCNT HTL. This bleach slowly rose over the 5 ns experimental window, indicating a diffusion-limited arrival of holes at the MAPbI₃/s-SWCNT interface. The near-identical kinetics of the (6,5) bleach growth and the MAPbI₃ bleach decay over the first approximately 3 ns indicate that the primary charge extraction process occurring over this temporal window was hole extraction into the HTL. At a delay of approximately 3 ns, the growth of the (6,5) S₁₁ bleach was complete, implying that (1) diffusion of holes to the SWCNT HTL and subsequent hole extraction was complete after approximately 3 ns, (2) the remaining signal at approximately 3 ns and beyond for the 750 nm MAPbI₃ bleach was

primarily or completely due to electrons, and (3) longer delays are required to follow either electron extraction by TiO_2 or recombination of extracted charges. The slow rise of the (6,5) S_{11} bleach was fitted to extract the kinetics of hole diffusion to this interface (thin solid trace, Figure 4c). This fit utilizes an analytical solution to the diffusion equation with an average
 5 lifetime of approximately 42 ns for holes in the MAPbI_3 layer. The fit yields a hole diffusion constant of $0.3 \text{ cm}^2/\text{s}$ and a diffusion length of approximately $1 \mu\text{m}$ for holes in the MAPbI_3 layer.

The electronic delay on the TA spectrometer used enabled carrier recombination in the $\text{TiO}_2/\text{MAPbI}_3/(6,5)$ trilayer over a $400 \mu\text{s}$ time window to be probed (see Figure 4d). The
 10 MAPbI_3 bleach (750 nm) decayed relatively quickly, and was fully recovered by about 400 ns, indicating that both electrons and holes were fully removed from the perovskite over this time frame. In stark contrast, the (6,5) S_{11} bleach (1000 nm) was extremely long-lived, and can be fit by a biexponential decay ($\tau_1 = 40 \mu\text{s}$ and $\tau_2 = 416 \mu\text{s}$, thick solid line). Figure 4d demonstrates that once holes were extracted by the SWCNT HTL, the resulting charge-
 15 separated state was extremely long-lived. PES measurements suggest that ground-state interfacial charge transfer induced an appreciable barrier of ca. 300 meV to the back-transfer of holes from s-SWCNTs to the perovskite (see Figures 8a and 8b). This suggests that the very slow loss of holes in the s-SWCNT HTL (see Figure 4d) is a beneficial result of this band bending within the s-SWCNT film. It is informative to compare the demonstrably
 20 efficient hole extraction of the s-SWCNT HTL over a 4 ns time window with the apparently inefficient extraction by the traditionally used spiro-MeOTAD HTL (see Figure 4a). For a similarly prepared $\text{MAPbI}_3/\text{spiro-MeOTAD}$ interface, it has been demonstrated by PES that band bending within the spiro film shows an opposite trend of that found in a s-SWCNT HTL (see Figures 8a and 8b). Thus, in contrast to the s-SWCNT HTL, the band bending in the
 25 spiro-MeOTAD HTL should not inherently promote movement of holes into the bulk of the transport layer and inhibition of back-transfer to the perovskite layer.

To probe electron injection into TiO_2 , the time-resolved microwave conductivity (TRMC) was studied as a sensitive probe of free charge carriers (see Figures 9a and 9b). In the TRMC measurement, the change in microwave probe power ($\Delta P/P$) is proportional to the
 30 yield of free charge carriers (Φ) multiplied by the sum of the carrier mobilities ($\Sigma\mu = \mu_e + \mu_h$): $\Delta P/P \propto \Phi\Sigma\mu$. The quantity of the yield-mobility product ($\Phi\Sigma\mu$) is used as a figure of merit to compare the charge generation efficiency amongst various samples, with the caveat that the mobility of carriers in all components (e.g. absorber layer, ETL, HTL, etc.) should be

considered. The fluence dependence and temporal evolution of $\Phi\Sigma\mu$ for four different MAPbI₃ samples is shown in Figures 9a and 9b. Figure 9a shows that $\Phi\Sigma\mu$ for all samples follows the same general trend with fluence, with an average value of approximately 10 cm²/Vs. This yield-mobility product is over an order of magnitude higher than $\Phi\Sigma\mu$ obtained for high internal quantum efficiency (ca. 70%) charge generation in s-SWCNT/C₆₀ donor/acceptor heterojunctions. This large difference in $\Phi\Sigma\mu$ suggests that the observed photoconductance is dominated by carrier(s) in the perovskite layer. Since TA measurements demonstrate that hole transfer to s-SWCNTs is complete by 3 ns, comparable to the pulse duration for the TRMC measurements, the similar yield-mobility products of the TiO₂/MAPbI₃ and TiO₂/MAPbI₃/s-SWCNT suggest that the dominant carrier that contributes to $\Phi\Sigma\mu$ is the perovskite electron (since removal of the hole does not affect $\Phi\Sigma\mu$). If $\Phi\Sigma\mu$ is considered to be dominated by the perovskite electron, then the similar yield-mobility products of the quartz/MAPbI₃ and TiO₂/MAPbI₃ samples suggest that negligible electron density is injected from MAPbI₃ into the TiO₂ ETL over the 4 ns TRMC pulse.

The TRMC transients for the same four samples are plotted in Figure 9b. The TRMC dynamics are similar for MAPbI₃ and TiO₂/MAPbI₃, suggesting that, in the absence of the s-SWCNT HTL, electron extraction by the compact TiO₂ ETL is inefficient even over a time frame of about 450 ns. In sharp contrast, samples with a s-SWCNT HTL exhibit significantly faster decay, corresponding to electron extraction (presumably diffusion-limited) over the 450 ns window. Similar to TA dynamics, the TRMC transient for the trilayer with an LV s-SWCNT HTL are commensurate with the (6,5) s-SWCNT HTL, suggesting that a broad range of s-SWCNTs with different band gaps can be used to enhance the charge extraction kinetics from the alkyl ammonium metal halide perovskite layer.

These results demonstrate that improved electron extraction can be achieved not only by the direct employment of an interfacial layer at the ETL interface, but also by better extraction of holes at the HTL interface. Figure 9b demonstrates that once holes are efficiently removed by the s-SWCNT HTL within about 3 ns, the concomitant increase of the quasi-Fermi level in the (now n-type) MAPbI₃ can provide the needed driving force for electron injection into the TiO₂ ETL. This result indicates that the rates for carrier extraction are dynamically dependent upon the configuration of interfaces within the device stack.

A kinetic scheme emerges from the detailed time-resolved measurements, as depicted in Figure 10a. Figure 10b summarizes the time scales of each process, along with the probe wavelength and spectroscopic measurement used to follow the processes. Carriers generated

in the alkyl ammonium metal halide perovskite layer recombine with average time constants of several tens of nanoseconds in the absence of the s-SWCNT HTL. Diffusion of holes to the SWCNT HTL occurs over the course of approximately 3 ns, with a diffusion constant of approximately $0.3 \text{ cm}^2/\text{Vs}$, where hole injection into the SWCNT HTL then occurs on a sub-
 5 picosecond time scale. Electron injection into the TiO_2 ETL is slower, and is observed (for samples with a s-SWCNT HTL) by the loss of 9 GHz absorption in the TRMC measurement over the course approximately 450 ns. Following extraction of both charge carriers into the respective transport layers, back-transfer (and subsequent recombination, not directly observed) is very slow. The time constant of back-transfer is in the range of 40 – 420 μs
 10 ($\lambda_{\text{probe}} = 1000 \text{ nm}$).

The fast charge extraction and very slow recombination observed above suggest that purely semiconducting SWCNT HTLs or interfacial layers could improve the performance of MAPbI_3 PV devices. With these considerations in mind, s-SWCNT films were tested as thin interfacial layers between a MAPbI_3 absorber layer and a traditional spiro-MeOTAD HTL
 15 (see Figure 11a) to improve hole extraction. In this role, the interfacial layer was very thin and did not provide a direct transport pathway to the charge collection electrode. Instead, the interfacial layer was used to establish the appropriate interfacial energetics that encouraged rapid charge extraction and slow recombination.

Figure 11b displays typical J-V curves for devices with either no interfacial layer or a
 20 5 nm (6,5) s-SWCNT interfacial layer. In addition to improved efficiency, the devices with s-SWCNT interfacial layers also demonstrated significantly reduced hysteresis with regards to forward and reverse voltage scans and improved stability (see Figure 12). The reduced hysteresis most likely stems from a reduced interfacial trapping probability for both holes and electrons, as the time-resolved measurements demonstrate efficient extraction of both charge
 25 carriers. The improvement in J_{sc} is directly reflected in an increase to the external quantum efficiency over the entire wavelength range captured by the MAPbI_3 absorber layer (see Figure 11c).

Table 1 summarizes the performance for a series of devices, prepared on top of an identical TiO_2 ETL, with different (6,5) s-SWCNT interfacial layer thicknesses. The device
 30 with the thinnest (6,5) s-SWCNT interfacial layers showed improved J_{sc} , V_{oc} , FF, and power conversion efficiency, and these improvements diminish with increasing s-SWCNT thickness. The average efficiency for devices utilizing a 5 nm (6,5) s-SWCNT interfacial layer was 16.1%, with a maximum efficiency of 16.5%, representing an approximate 2%

increase in the absolute efficiency over reference devices. While all device parameters improved, the largest improvements were seen for J_{sc} and FF. As expected from the similarity in charge extraction kinetics for (6,5) and LV s-SWCNTs (see Figures 4a and 9b), devices prepared with LV s-SWCNT interfacial layers showed the same improvements observed for the (6,5) interfacial layers.

It is important to note that the s-SWCNTs in these interfacial layers play very different roles compared to devices utilizing thick SWCNT HTLs (within insulating matrices) to provide direct transport pathways from MAPbI₃ to a metal electrode. In the examples provided herein, thick (~200 nm) layers of the *doped* spiro-MeOTAD HTL are used. The very thin (and *purely semiconducting*) SWCNT layers have low surface roughness (< 5 nm), so there are very few, if any, SWCNT bundles that provide a direct transport pathway between the MAPbI₃ absorber layer and the metal electrode. Instead, the TA/TRMC results covered here suggest that the s-SWCNT interfacial layers most likely improve efficiency by establishing the appropriate interfacial energetics to facilitate fast hole extraction and slow recombination.

Table 1. Device parameters for MAPbI₃ solar cells prepared on an identical TiO₂ ETL and capped with a spiro-MeOTAD HTL. The devices either contained no interfacial layer or utilized (6,5) s-SWCNT interfacial layers with various thicknesses. For control devices, prepared with no interfacial layer, the MAPbI₃ surface was treated with toluene via ultrasonic spray-coating, in similar fashion to the (6,5) s-SWCNT deposition step.

Interfacial Layer	J_{sc} (avg) mA/cm ²	V_{oc} (avg) V	FF (avg)	PCE (avg) %	PCE (max) %
none	19.9 ± 0.2	1.04 ± 0.02	0.68 ± 0.03	14.1 ± 0.4	14.7
(6,5) 5 nm	20.8 ± 0.3	1.07 ± 0.009	0.73 ± 0.02	16.1 ± 0.3	16.5
(6,5) 10 nm	20.0 ± 0.3	1.06 ± 0.002	0.71 ± 0.02	15.0 ± 0.2	15.2
(6,5) 15 nm	19.4 ± 0.5	1.03 ± 0.002	0.65 ± 0.04	13.1 ± 0.6	13.7
LV 5 nm	21.1 ± 0.1	1.03 ± 0.003	0.73 ± 0.006	15.9 ± 0.2	16.1
LV 10 nm	21.4 ± 0.3	1.03 ± 0.004	0.68 ± 0.008	14.9 ± 0.3	15.2
LV 15 nm	21.7 ± 0.1	1.01 ± 0.002	0.60 ± 0.006	13.2 ± 0.2	13.3
None/toluene	20.5 ± 0.03	1.05 ± 0.006	0.66 ± 0.04	14.23 ± 0.8	14.8

This work demonstrates, for a technologically relevant perovskite PV device stack, that the narrow material-specific spectroscopic signatures of a charged s-SWCNT HTL can

be used to unambiguously track the kinetics of critical processes, such as carrier diffusion, interfacial charge transfer, and recombination. Importantly, highly enriched semiconducting SWCNT HTLs or interfacial layers provide orders-of-magnitude temporal separation for the charge extraction and recombination rates. The connection of our time-resolved spectroscopic measurements to improved device efficiencies provides a direct link between the improved charge extraction and slow recombination observed in our time-resolved measurements and the PV device performance that depends sensitively on the kinetics of these processes. The results presented herein indicate that thin s-SWCNT interfacial layers may represent an economical way to improve perovskite solar cell performance for a variety of HTLs.

Experimental Methods

Perovskite film preparation: Fluorine-doped tin oxide (FTO, TEC15, Hartford, IN) was cleaned by an overnight base bath soaking (5 wt% NaOH in ethanol). A compact TiO₂ layer was deposited by spray pyrolysis of 0.2 M titanium diisopropoxide bis(acetylacetonate) in 1-butanol solution at 450 °C. A modified method based on the solvent engineering approach was used to deposit perovskite film. Therein the precursor was made of 44 wt% of 1:1 molar ratio of MAI and PbI₂ in γ -Butyrolactone (GBL, Aldrich)/dimethyl sulfoxide (DMSO, Sigma-Aldrich) (7/3 v/v). The substrates were spun at 4500 rpm for 50 seconds with a drop of toluene being casted during the spinning. The perovskite film was fully crystallized by annealing at 85 °C for 10 minutes. Perovskite films on glass substrates for the TAS control measurements were prepared in the same manner except without the TiO₂ spray pyrolysis process.

Single-walled carbon nanotube layer preparation: CoMoCat SG65i SWCNTs were purchased from Southwest Nanotechnologies, Inc., and PFO-BPy was purchased from American Dye Source. Laser vaporization (LV) nanotubes were synthesized in house at a synthesis temperature of 1125 °C. SWCNTs were dispersed at a loading of ~1 mg/mL in ~2.5 mg/mL PFO-BPy in toluene (10 – 15 mL total volume) through tip sonication for 30 minutes (Cole-Palmer CPX 750) in a bath of cool (18°C) flowing water. Following sonication, undispersed material was removed by ultracentrifugation for 5 minutes using an SW32Ti motor (Beckman) at 13,200 rpm and 20°C. The supernatant was retained, and several of these supernatants were combined to produce larger volumes. To remove excess polymer, these larger volumes (30 – 35 mL) were centrifuged for 20 hours at 24,100 rpm and 0°C. In this case, the resulting supernatant (containing excess polymer unbound to SWCNTs) was discarded and the pellet containing (6,5) or LV SWCNT material was redispersed in toluene.

This polymer removal process was repeated until a SWCNT:PFO-BPy mass ratio of ~1:1 was obtained. (6,5) and LV SWCNT thin films with thicknesses in the range of ~10 nm were prepared through ultrasonic spray deposition onto the MAPbI₃ films (or other substrates) using a dispersion flow rate of 0.25 mL/min and gas flow rate of 7.0 std L/min. The nozzle power was fixed at 0.8 W and the substrate was heated to 130°C to allow for evaporation of the solvent. After spraying, the films were soaked in a toluene bath (80°C) to remove some residual polymer and better couple SWCNTs within the film. To avoid potential photo-degradation during the TA experiments, the films were introduced into a helium glovebox and another quartz slide was sealed on top of the sample using a polymer film (Surlyn, Solaronix) heated to 90°C. The polymer was cut into a hollow frame so that it only sealed the outer edges of the slide and did not interfere with the sample. Note that for these spectroscopic measurements the stack was not completed with a final metal contact on top of the HTL which had no significant effect on hole extraction at the MAPbI₃/HTL interface.

Steady-state absorbance measurements: UV-vis absorbance measurements were carried out using a Cary6000i spectrophotometer equipped with the diffuse reflectance accessory. For each sample, transmission (T) and reflectance (R) were collected from 1800-200 nm with light incident on the quartz/TiO₂ interface. The absorbance was calculated according to $A = -\log(T+R)$.

Femtosecond transient absorption measurements: Femtosecond pump-probe TA experiments were carried out on a system that utilizes a 1-kHz regeneratively amplified Ti:Sapphire laser system (Coherent Libra) that produces laser pulses (100 fs, 4 mJ) at 800 nm. The Ti:Sapphire laser pumps an optical parametric amplifier (OPA) to generate 400 nm light, which was chopped at a rate of 500 Hz and used as the excitation pump pulse. The pump fluence was in the range of $\sim 5 \times 10^{13}$ and $\sim 3 \times 10^{12}$ photons pulse⁻¹ cm⁻² for near-IR and visible probe measurements, respectively. Continuum probe pulses (in the range of 800 nm – 1700 nm for near-IR and 400 nm – 800 nm for visible) were generated by passing a portion of the amplified 800 nm light through a sapphire plate. For “short-delay” experiments ($t_{\text{delay}} \leq 5$ ns), the probe pulse was delayed in time with respect to the pump pulse using a motorized translation stage mounted with a retro-reflecting mirror. For 0.1 ns to μ s experiments, a separate probe source (EOS, Ultrafast Systems) was used that can be electronically delayed with respect to the fs pump. This source was a VIS/NIR broadband continuum that allowed for seamless connection between data from time delays on the fs/ps

to ~0.5 ms time scale. No change in sample position or excitation conditions was required for switching between the two modes of probing.

Pump and probe beams were spatially overlapped at the quartz slide, and the sample was excited either through the SWCNT or perovskite layer first. For most measurements, we
 5 excited through the perovskite layer first, and we refer to this direction as “backside” illumination. This study focused primarily on backside illumination, since this illumination direction mimics the illumination in a typically prepared perovskite solar cell, and also allows us to generate excitons/carriers primarily in the perovskite layer. To confirm this, control studies were performed on neat SWCNT films, exciting the SWCNTs with a fluence that
 10 matched that reaching the perovskite/SWCNT interface following exponential decay through the ~240 nm thick perovskite layer (and any reflection). See Figure 13 for this control experiment. Figures 14a and 14b display an example of a frontside illumination experiment. Typical averaging times for data collection were 5-8 seconds, at each pump-probe delay, to achieve high signal-to-noise. The instrument response function (IRF) was ~120 fs.

Flash-photolysis time-resolved microwave conductivity: TRMC probes the generation and decay of free charge carriers by measuring the time-dependent absorption of a 9 GHz microwave probe by a photoexcited sample. Flash photolysis time resolved microwave conductivity (fp-TRMC) measurements were performed using a pulsed Q-switched Nd:YAG laser (3-5 ns pulses, Continuum Powerlite) and an optical parametric
 20 oscillator (Continuum Panther) pumped by the third harmonic (355 nm). Bilayer and neat films on quartz substrates were placed in an X-band microwave cavity to monitor the transient change in microwave power, $\Delta P(t)$. In all TRMC measurements, the excitation direction was through the quartz slide (backside illumination). In all TRMC measurements, the sample cavity was actively purged with dry nitrogen gas to maintain an inert environment and avoid photo-degradation. The transient change in the microwave power is related to the
 25 transient change in photoconductance, $\Delta G(t)$, by:

$$\Delta G(t) = \frac{1}{K} \frac{\Delta P(t)}{P} \quad (1)$$

In Equation 1, K is an experimental sensitivity factor of the measurement, which depends on the dimensions of the waveguide, the conductivity of the inner walls of the
 30 waveguide, and the dielectric properties of the sample loaded into the waveguide. The magnitude of ΔG following photoexcitation is proportional to the photo-generated free carrier

generation yield (ϕ) and the sum of the high-frequency free carrier mobilities ($\Sigma\mu$) by the following:

$$\eta G = q_e \cdot I_0 F_A \cdot \beta \quad (2)$$

In Equation 2, $\beta = 2.2$ and represents the ratio between the long (2.286 cm) and short (1.016 cm) axes of the microwave waveguide, q_e is the elementary charge, I_0 is the incident photon flux, and F_A is the fractional light absorption (determined from film absorbance).

[0001] Solar cell fabrication and characterization: Fluorine-doped tin oxide (FTO, TEC15, Hartford, IN) was patterned by a wet etching (5M hydrochloric acid and zinc powder), followed by an overnight base bath (5 wt% NaOH in ethanol). A compact TiO_2 layer was deposited by a spray pyrolysis of 0.2 M titanium diisopropoxide bis(acetylacetonate) in 1-butanol solution at 450°C. An antisolvent fast crystallization method was used to deposit perovskite film. Precursor was made of 1.4M equimolar MAI and PbI_2 in γ -Butyrolactone (GBL, Aldrich)/dimethyl sulfoxide (DMSO, Sigma-Aldrich) (7/3 v/v). Substrate was spun at 4000rpm for 50s, and a drop of toluene was casted during the spinning. Perovskite film was fully crystallized by annealing at 85°C for 10 minutes. The SWCNT interfacial layers were sprayed on top of the MAPbI_3 layer right after the fabrication of the MAPbI_3 film. The doped spiro-MeOTAD hole transport layer (HTL) was spin-coated on top of SWCNT-modified perovskite at 4,000 rpm for 35 seconds with a HTL solution, which includes of 80 mg 2,2',7,7'-tetrakis(N,N-dip-methoxyphenylamine)-9,9'-spirobifluorene (Spiro-MeOTAD; Merck), 30 μl bis(trifluoromethane) sulfonimide lithium salt stock solution (500 mg Li-TFSI in 1 ml acetonitrile), and 30 μl 4-tert-butylpyridine (TBP), and 1 ml chlorobenzene solvent. Finally a 150 nm Ag layer was deposited on the HTL layer by thermal evaporation.

The J-V characteristics of the cells were measured by a 2400 SourceMeter (Keithley) under simulated one-sun AM 1.5G illumination (100 mW cm^{-2}) (Oriel Sol3A Class AAA Solar Simulator, Newport Corporation). A shadow mask with 0.12 cm^2 active area was used for the measurement. External quantum efficiency (EQE) measurements were carried out by a solar cell quantum efficiency measurement system (QEX10, PV Measurements). For stability measurements (Figure 12), samples were stored in a glovebox in ambient light between measurements. The samples were taken out into ambient lab conditions (relative humidity between 15% and 40%) for J-V characterization each 3 – 4 days. Solar cell characterization took approximately one hour, after which samples were returned to the glovebox.

The foregoing discussion and examples have been presented for purposes of illustration and description. The foregoing is not intended to limit the aspects, embodiments, or configurations to the form or forms disclosed herein. In the foregoing Detailed Description for example, various features of the aspects, embodiments, or configurations are grouped together in one or more embodiments, configurations, or aspects for the purpose of streamlining the disclosure. The features of the aspects, embodiments, or configurations, may be combined in alternate aspects, embodiments, or configurations other than those discussed above. This method of disclosure is not to be interpreted as reflecting an intention that the aspects, embodiments, or configurations require more features than are expressly recited in each claim. Rather, as the following claims reflect, inventive aspects lie in less than all features of a single foregoing disclosed embodiment, configuration, or aspect. While certain aspects of conventional technology have been discussed to facilitate disclosure of some embodiments of the present disclosure, the Applicants in no way disclaim these technical aspects, and it is contemplated that the claimed invention may encompass one or more of the conventional technical aspects discussed herein. Thus, the following claims are hereby incorporated into this Detailed Description, with each claim standing on its own as a separate aspect, embodiment, or configuration.

CLAIMS

What is claimed is:

1. A device comprising:
an alkyl ammonium metal halide perovskite layer; and
5 a nanostructured semiconductor layer in physical contact with the alkyl ammonium metal halide perovskite layer.
2. The device of claim 1, wherein the alkyl ammonium metal halide perovskite layer comprises methyl ammonium cations.
3. The device of either claim 1 or 2, wherein the alkyl ammonium metal halide
10 perovskite layer comprises anions of at least one of chlorine, bromine, astatine, or iodine.
4. The device of any one of claims 1 through 3, wherein the alkyl ammonium metal halide perovskite layer comprises cations of a metal in a 2+ valence state.
5. The device of claim 4, wherein the metal comprises at least one of lead, tin, or germanium.
- 15 6. The device of any one of claims 1 through 5, wherein the nanostructured semiconductor layer comprises a plurality of an organic nanostructure.
7. The device of claim 6, wherein the organic nanostructure comprises at least one of carbon nanotubes, graphene quantum dots, or carbon dots.
8. The device of claim any one of claims 1 through 5, wherein the nanostructured
20 semiconductor layer comprises a plurality of an inorganic nanostructure.
9. The device of claim 8, wherein the inorganic nanostructure comprises a transition metal dichalcogenide.
10. The device of claim 8, wherein the inorganic nanostructure comprises at least one of phosphine, silicone, or germanene.
- 25 11. The device of claim 8, wherein the inorganic nanostructure comprises at least one of quantum dots, nanorods, nanowires, or nanosheets.
12. The device of claim 11, wherein the inorganic nanostructure comprises at least one of CdS, CdSe, PbSe, InAs, InP, or InSb.

13. The device of any one of claims 1 through 12, further comprising a hole transport layer, wherein:

the nanostructured semiconductor layer is positioned between the hole transport layer and the alkyl ammonium metal halide perovskite layer, and

5 the nanostructured semiconductor layer is in physical contact with the hole transport layer.

14. The device of claim 13, wherein the hole transport layer comprises at least one of spiro-MeOTAD, polyhexyl (3-thiophene), or an inorganic oxide.

15. The device of either one of claims 13 or 14, further comprising a conducting layer
10 positioned above the hole transport layer.

16. The device of claim 15, further comprising an electron transport layer, wherein the alkyl ammonium metal halide perovskite layer is positioned between the hole transport layer and the electron transport layer.

17. The device of claim 16, further comprising a transparent conducting oxide layer
15 positioned below the electron transport layer.

18. The device of claim 17, further comprising a substrate positioned below the transparent conducting oxide layer.

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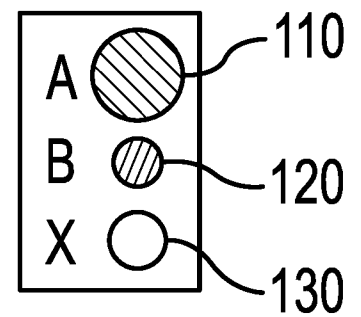
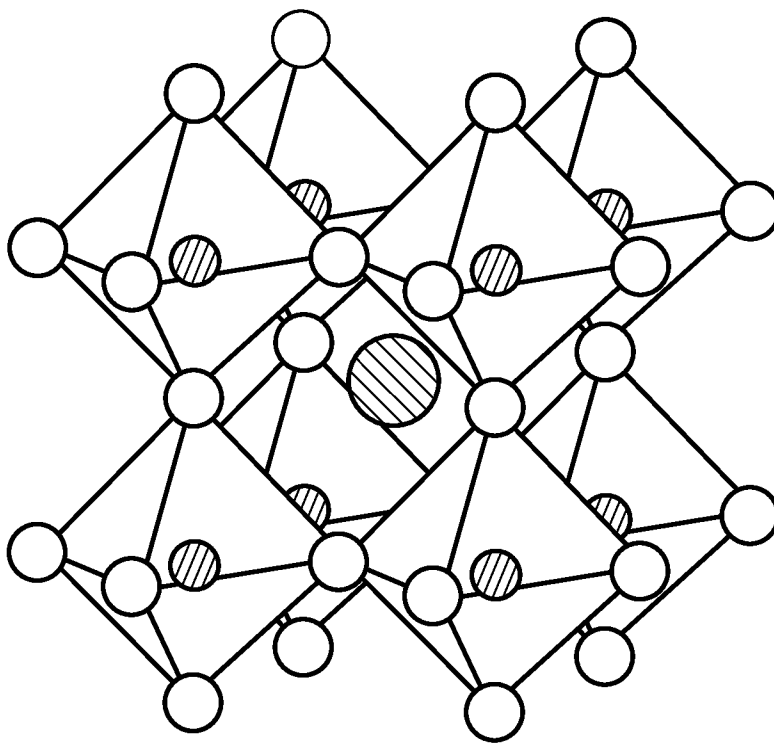



Figure 1

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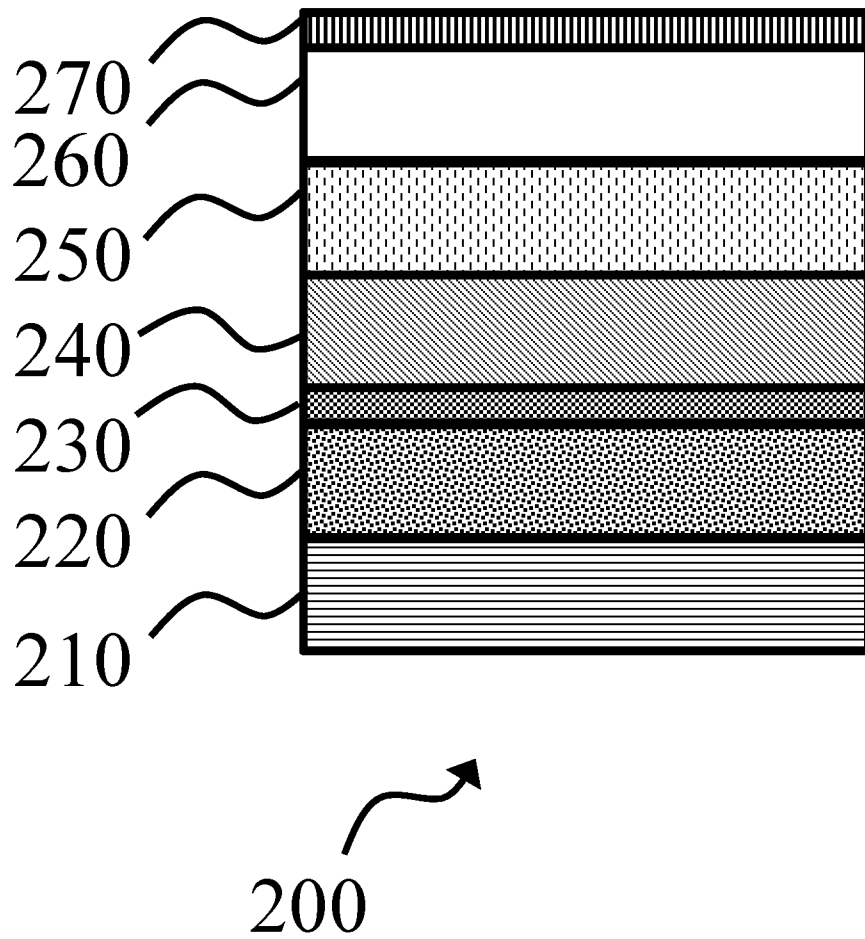


Figure 2

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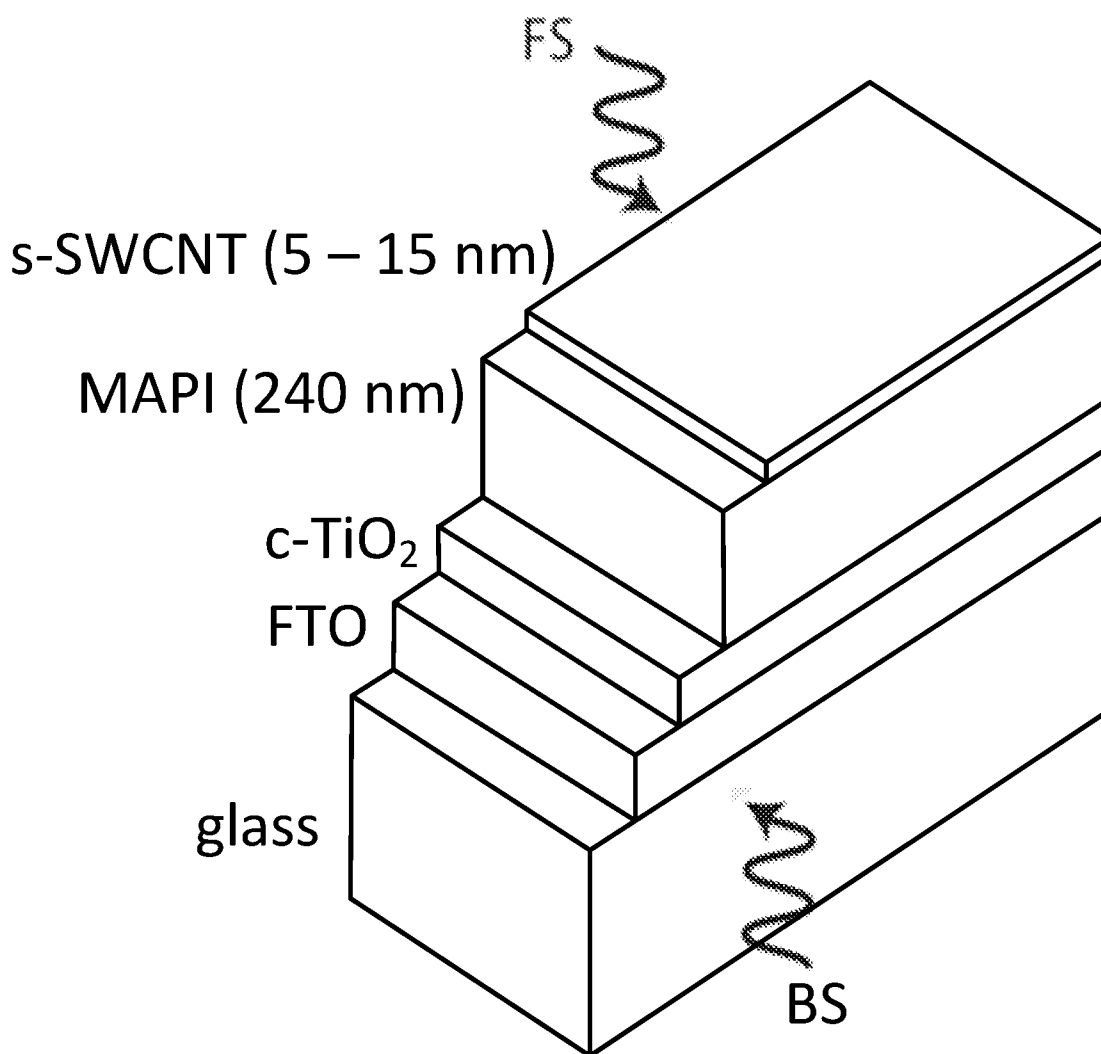


Figure 3a

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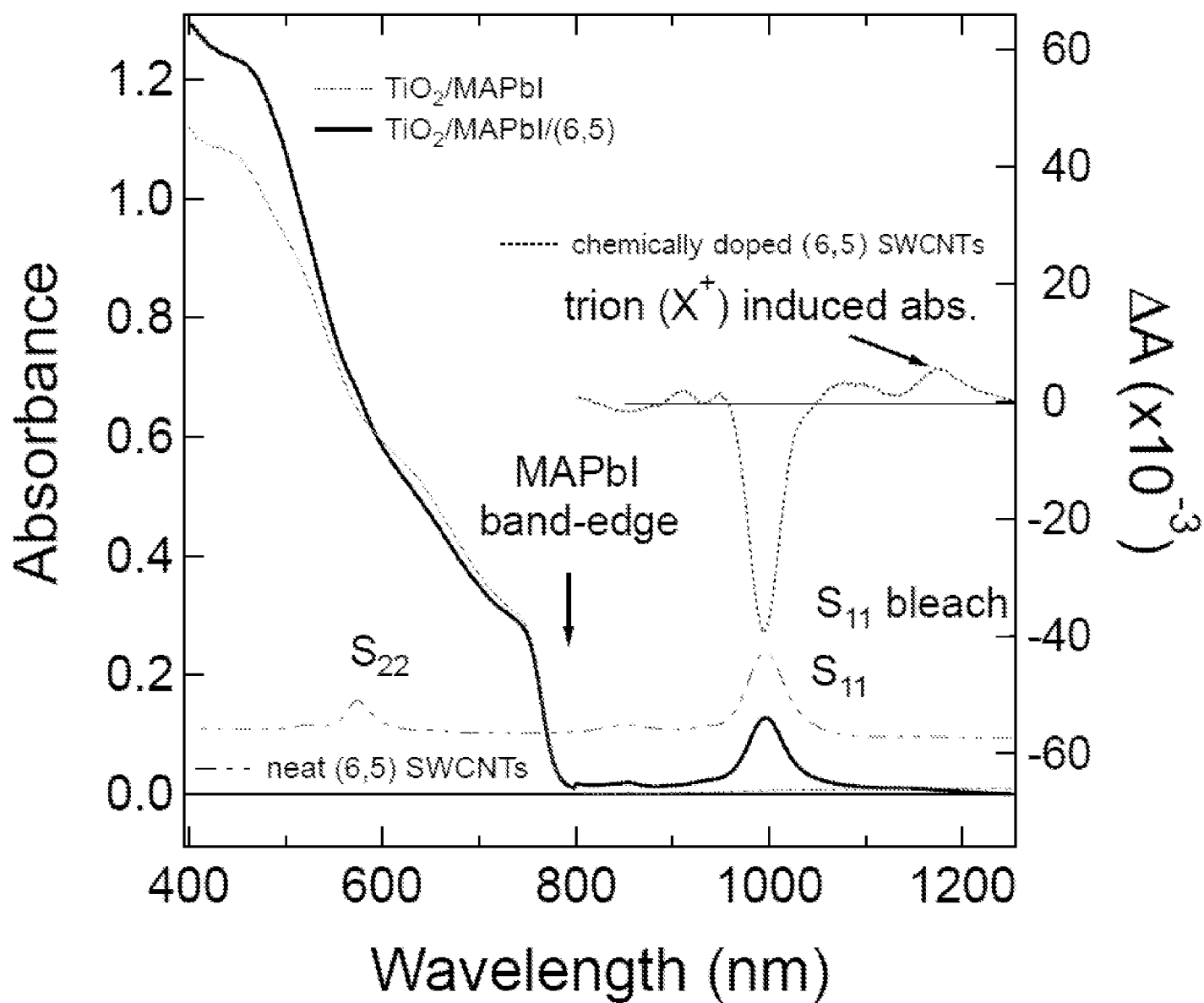


Figure 3b

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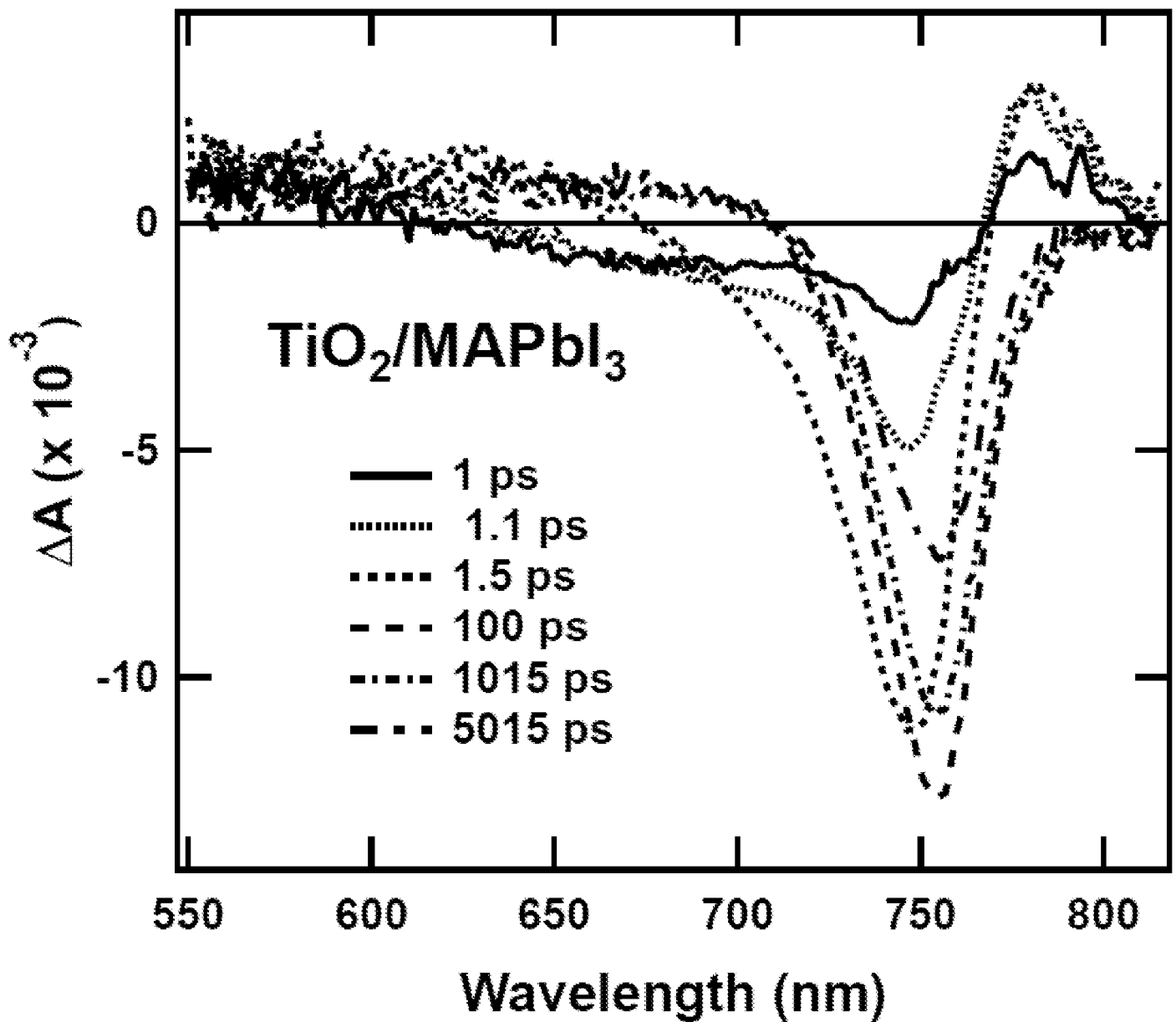


Figure 3c

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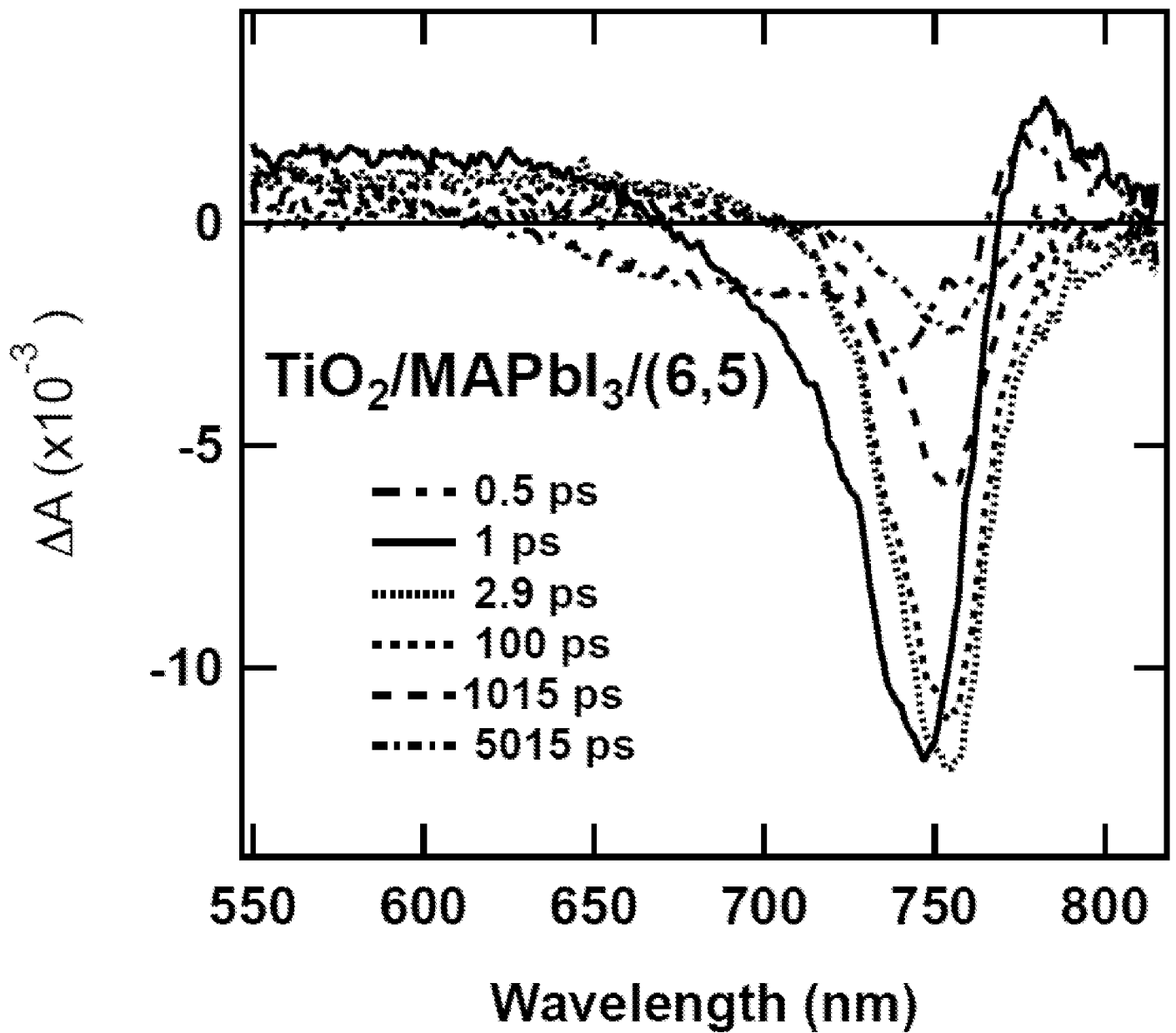


Figure 3d

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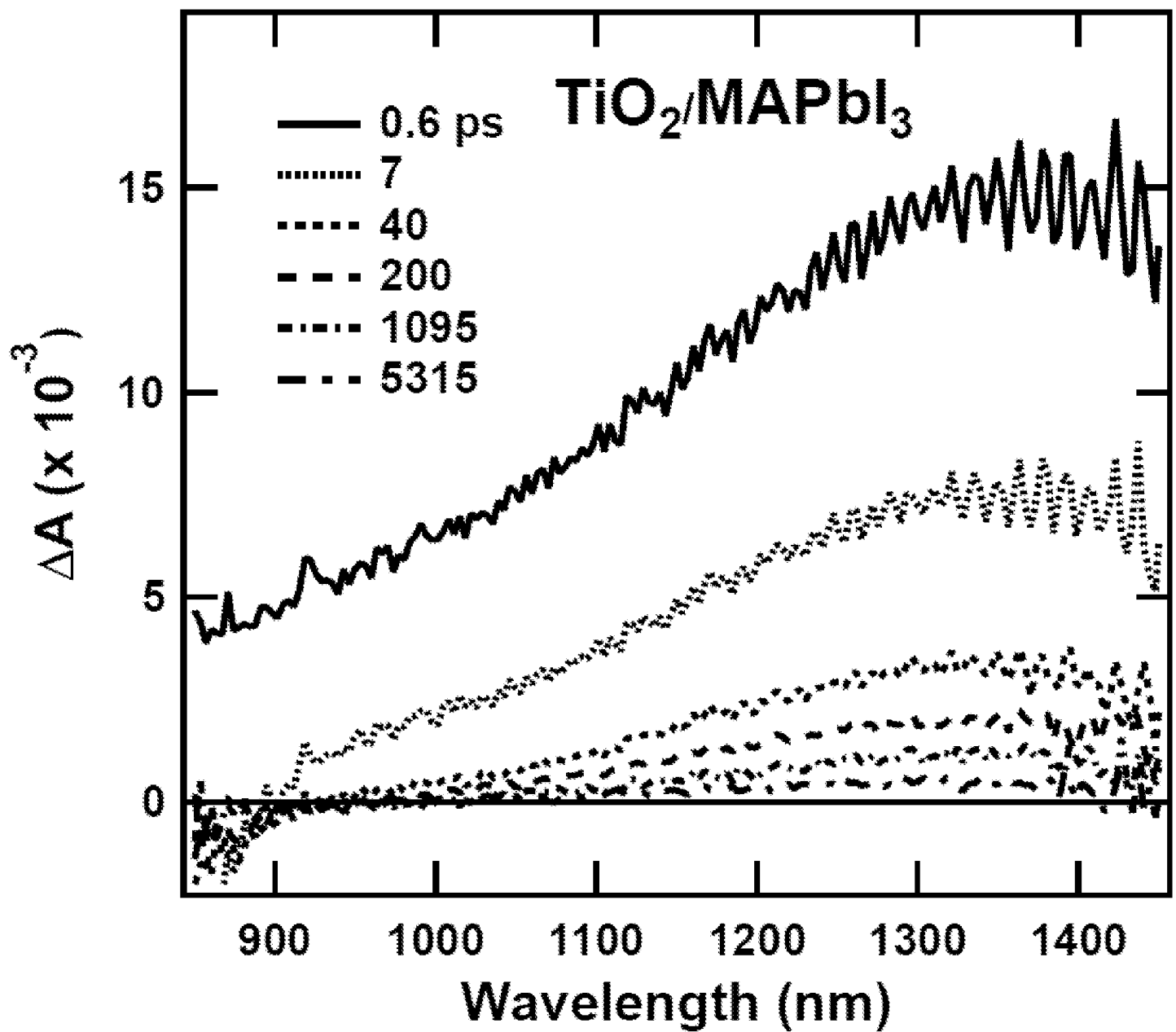


Figure 3e

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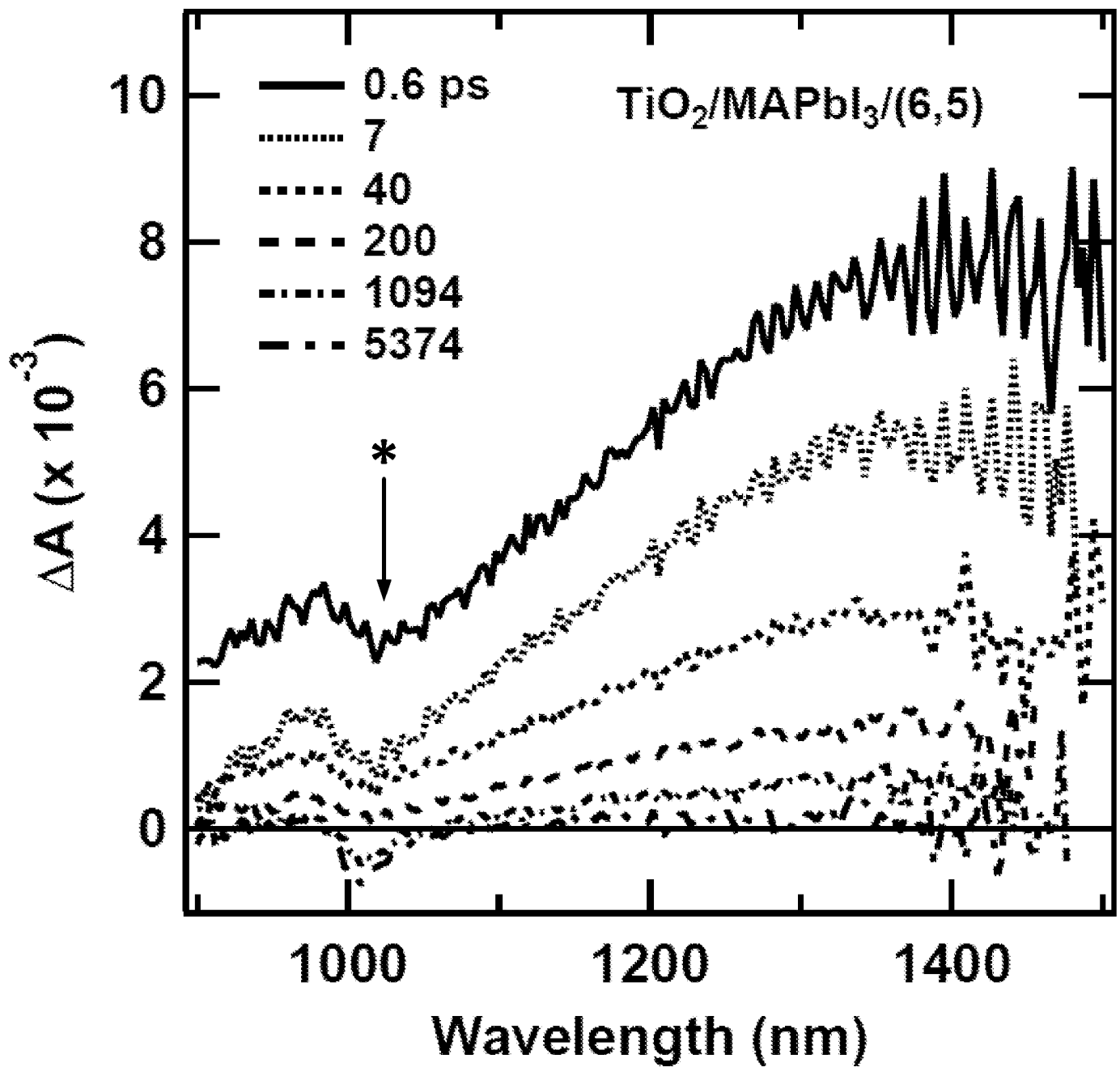


Figure 3f

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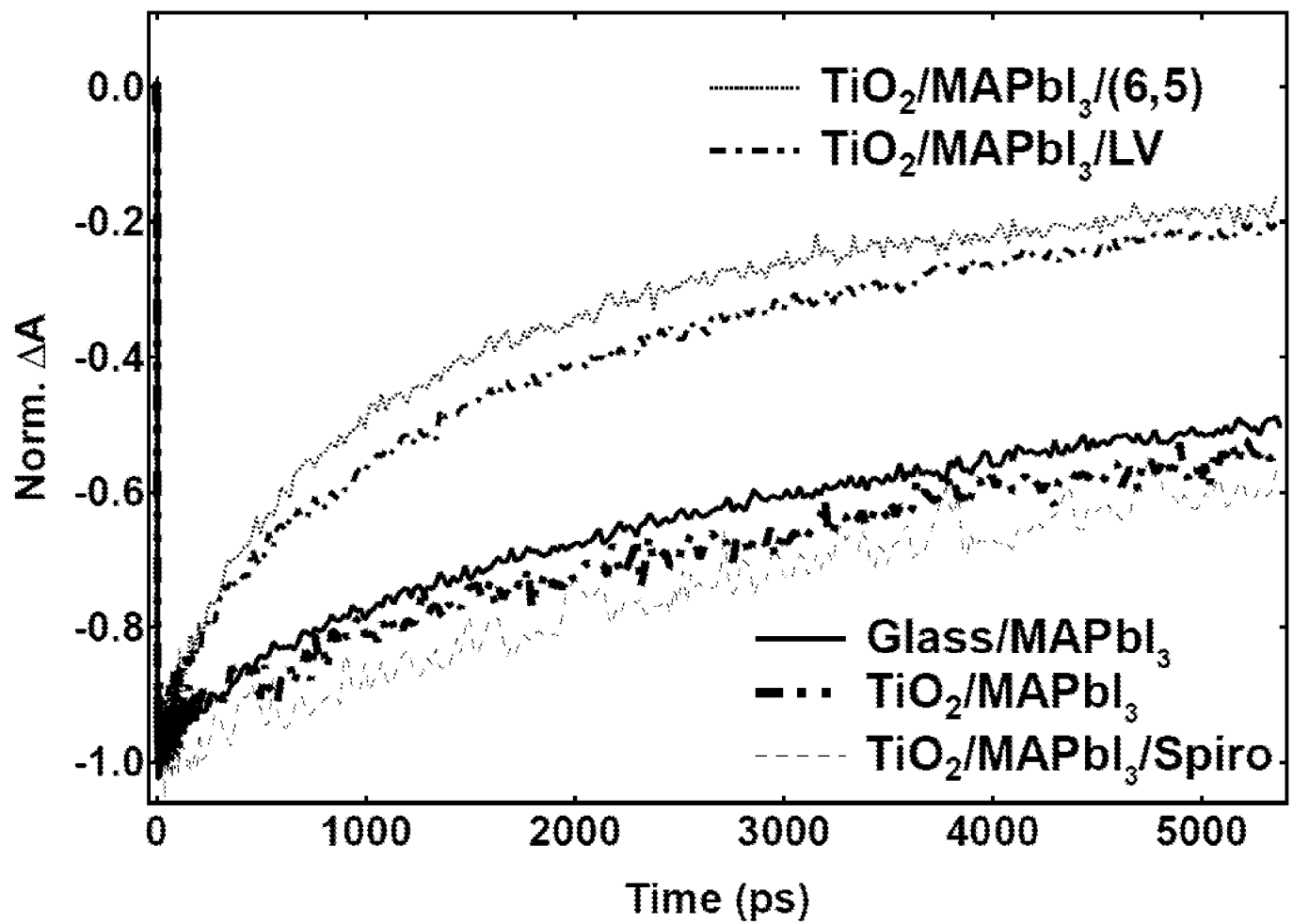


Figure 4a

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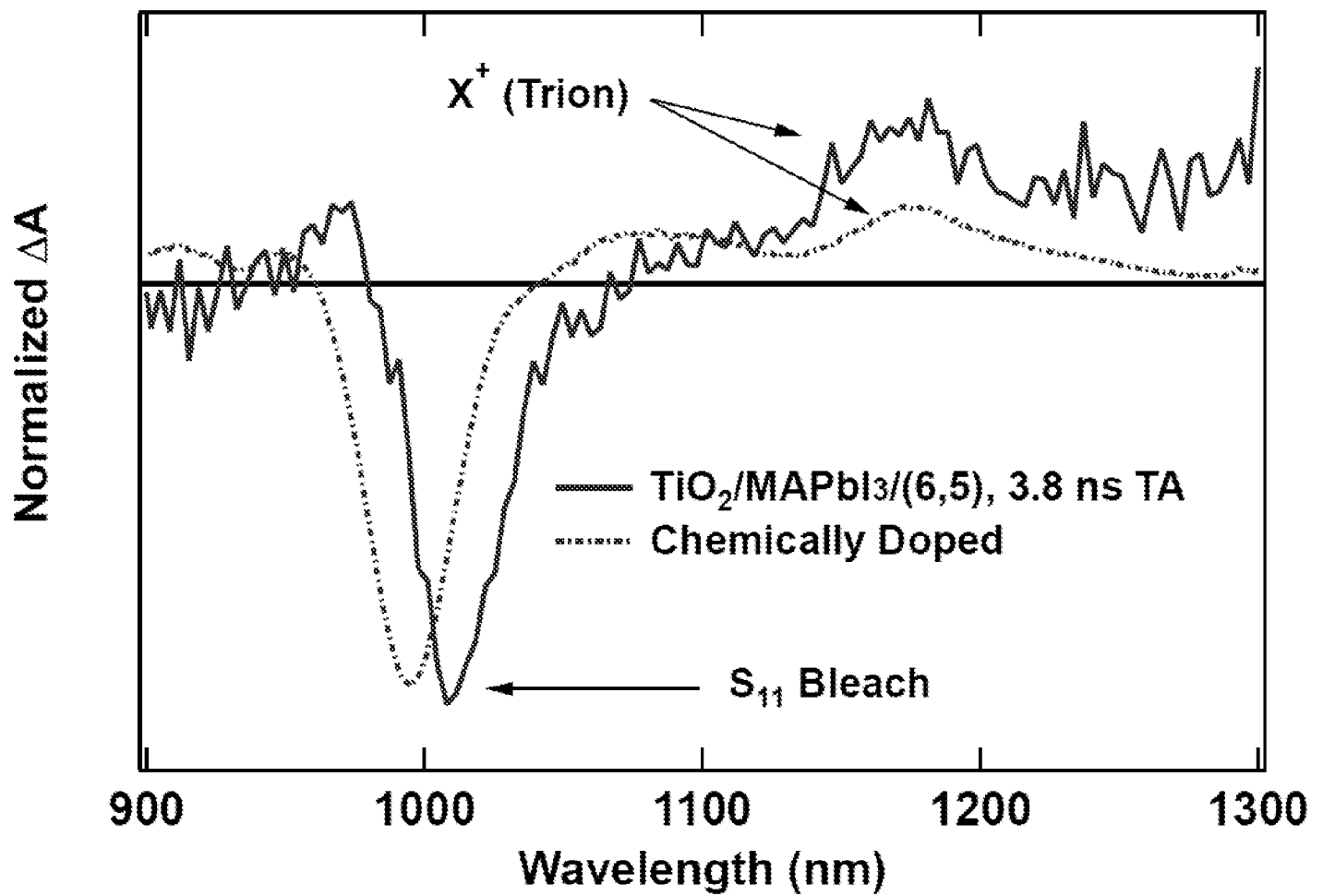


Figure 4b

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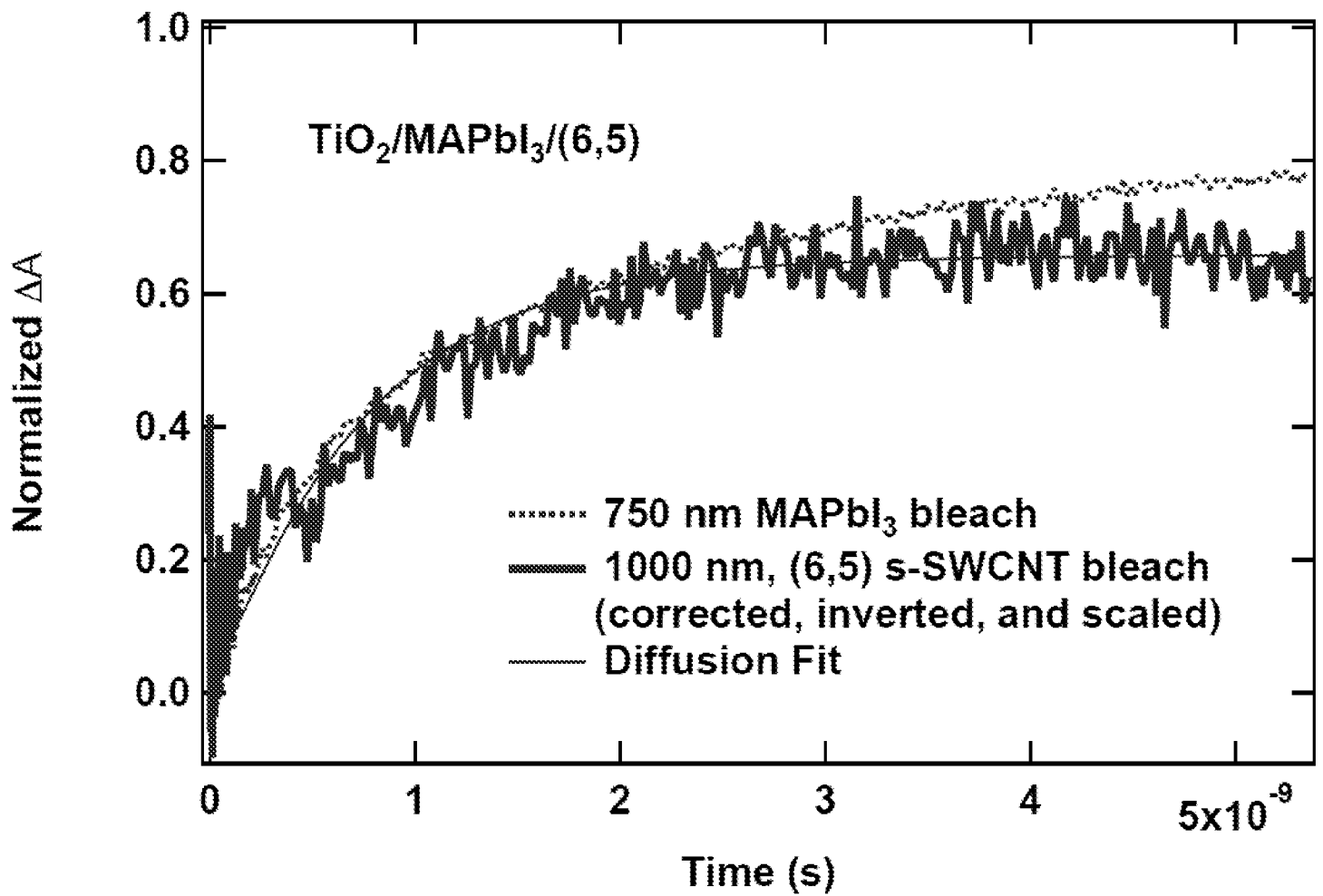


Figure 4c

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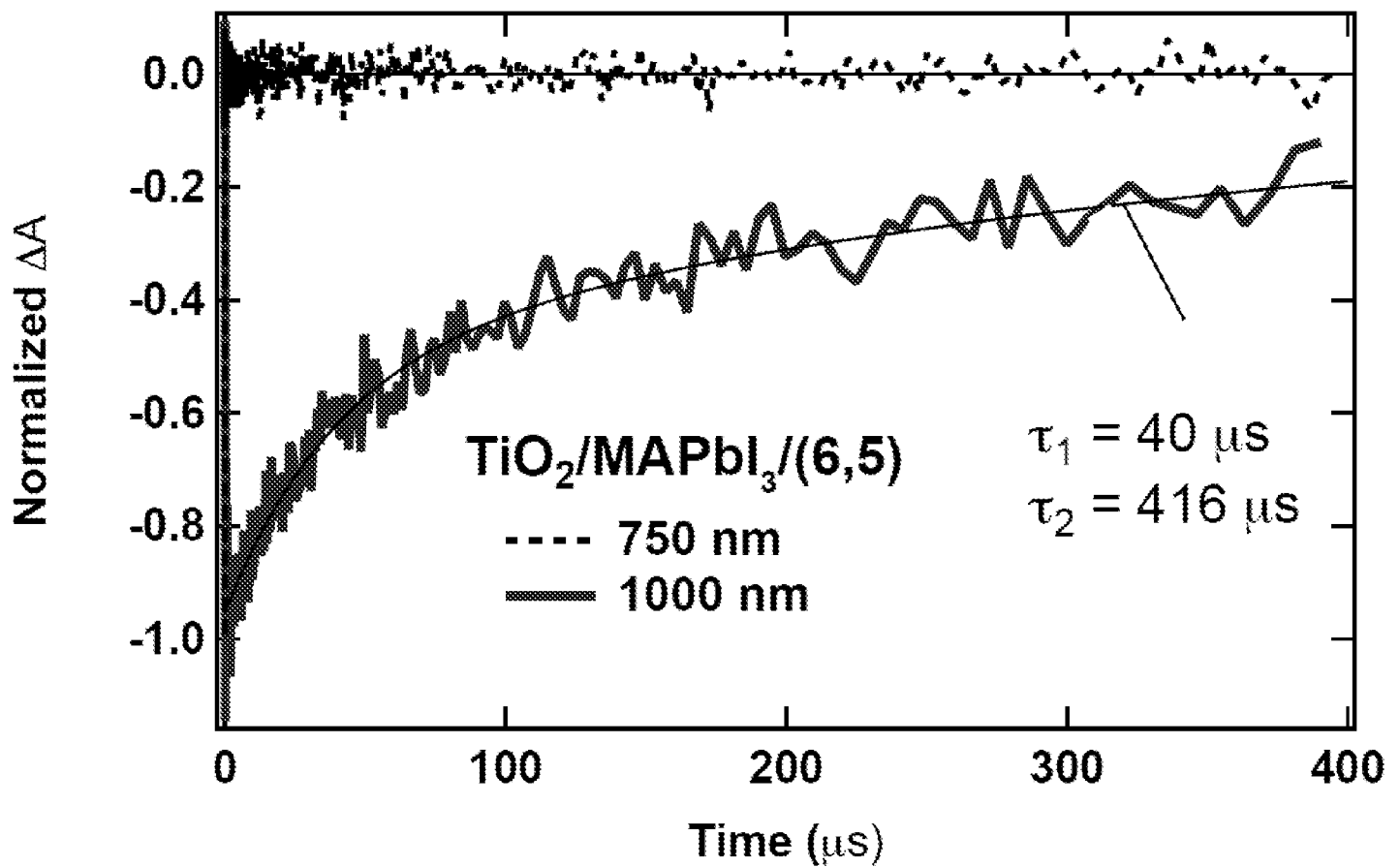
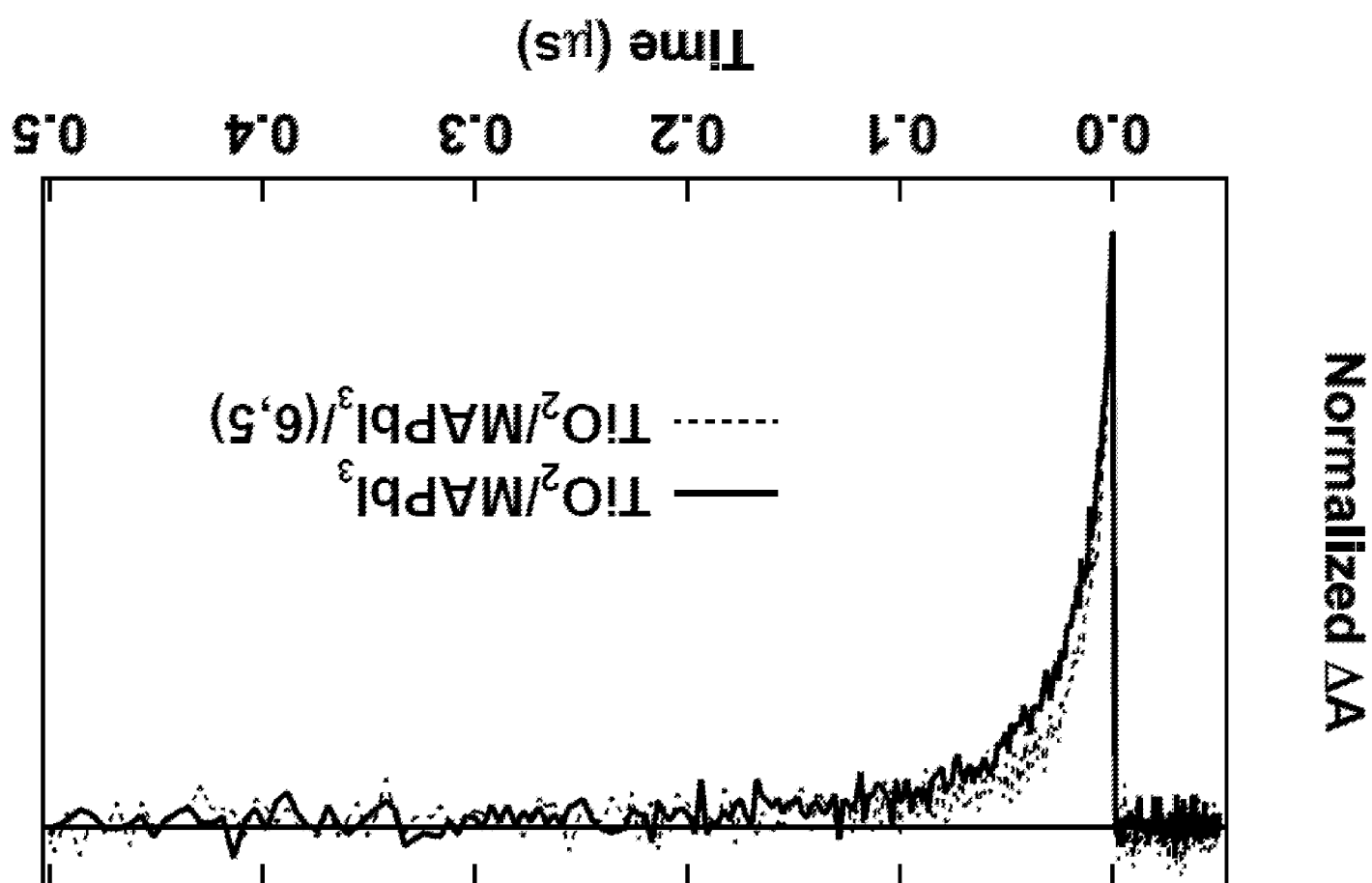


Figure 4d

Figure 5



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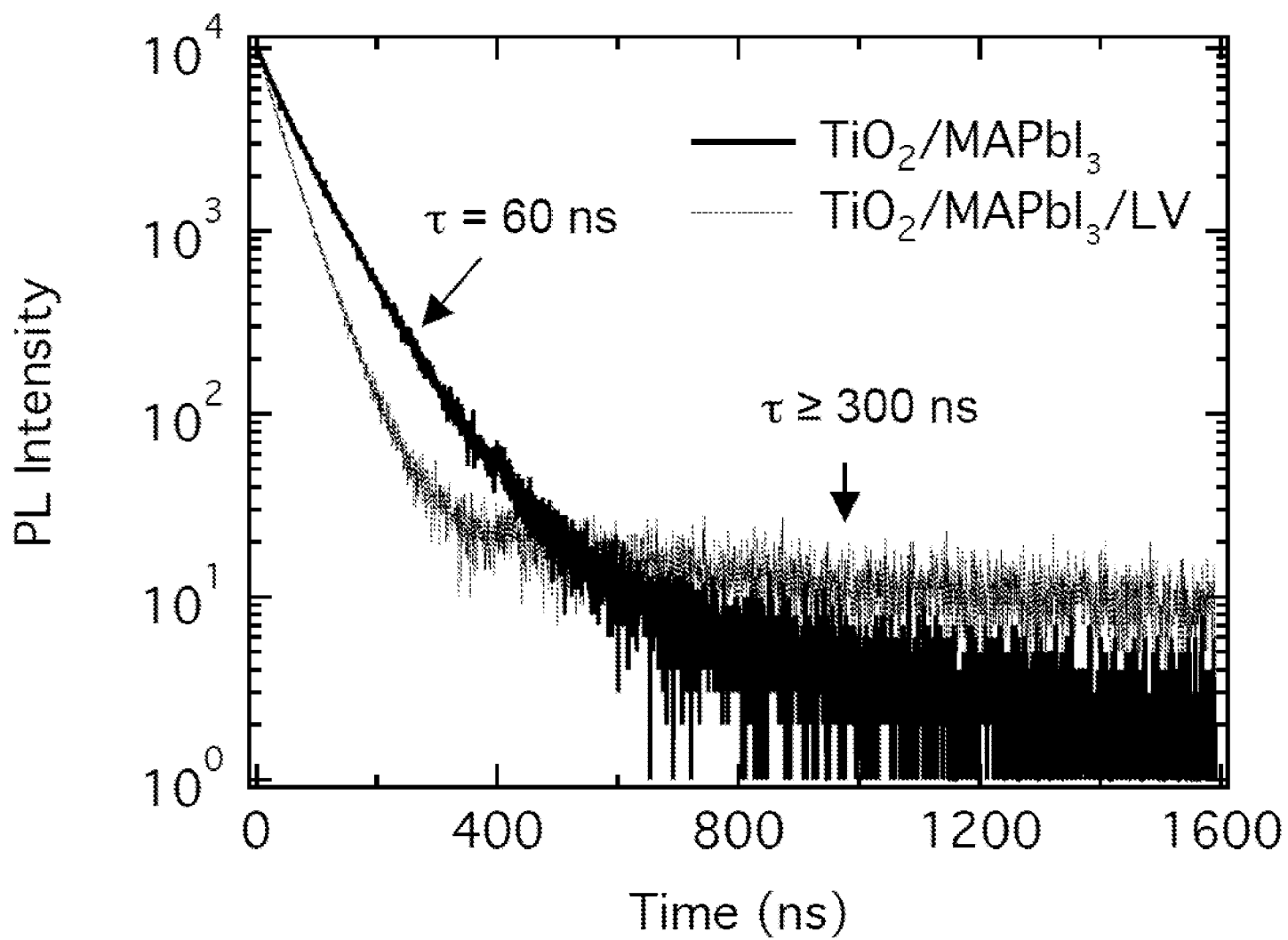


Figure 6

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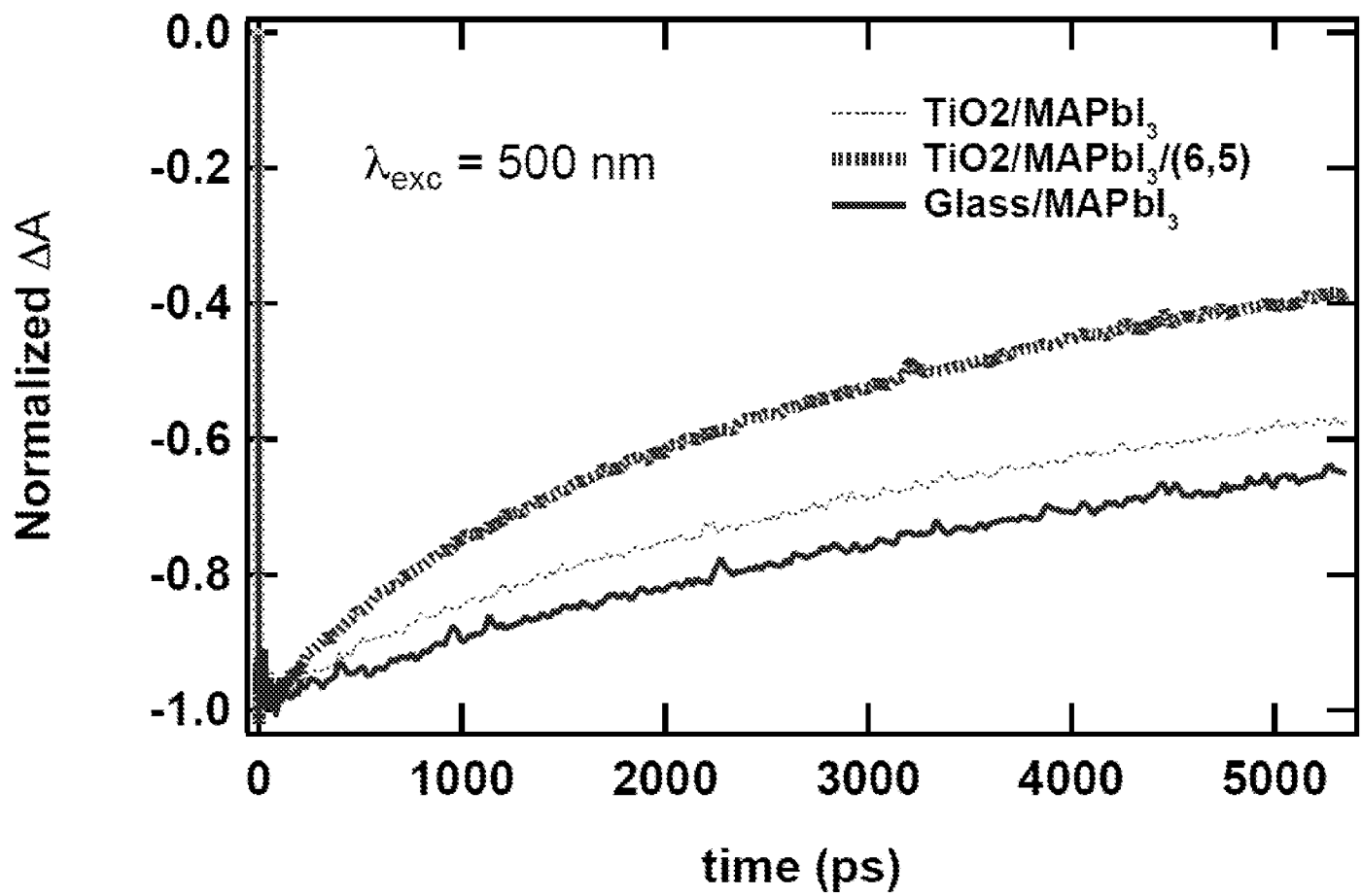


Figure 7a

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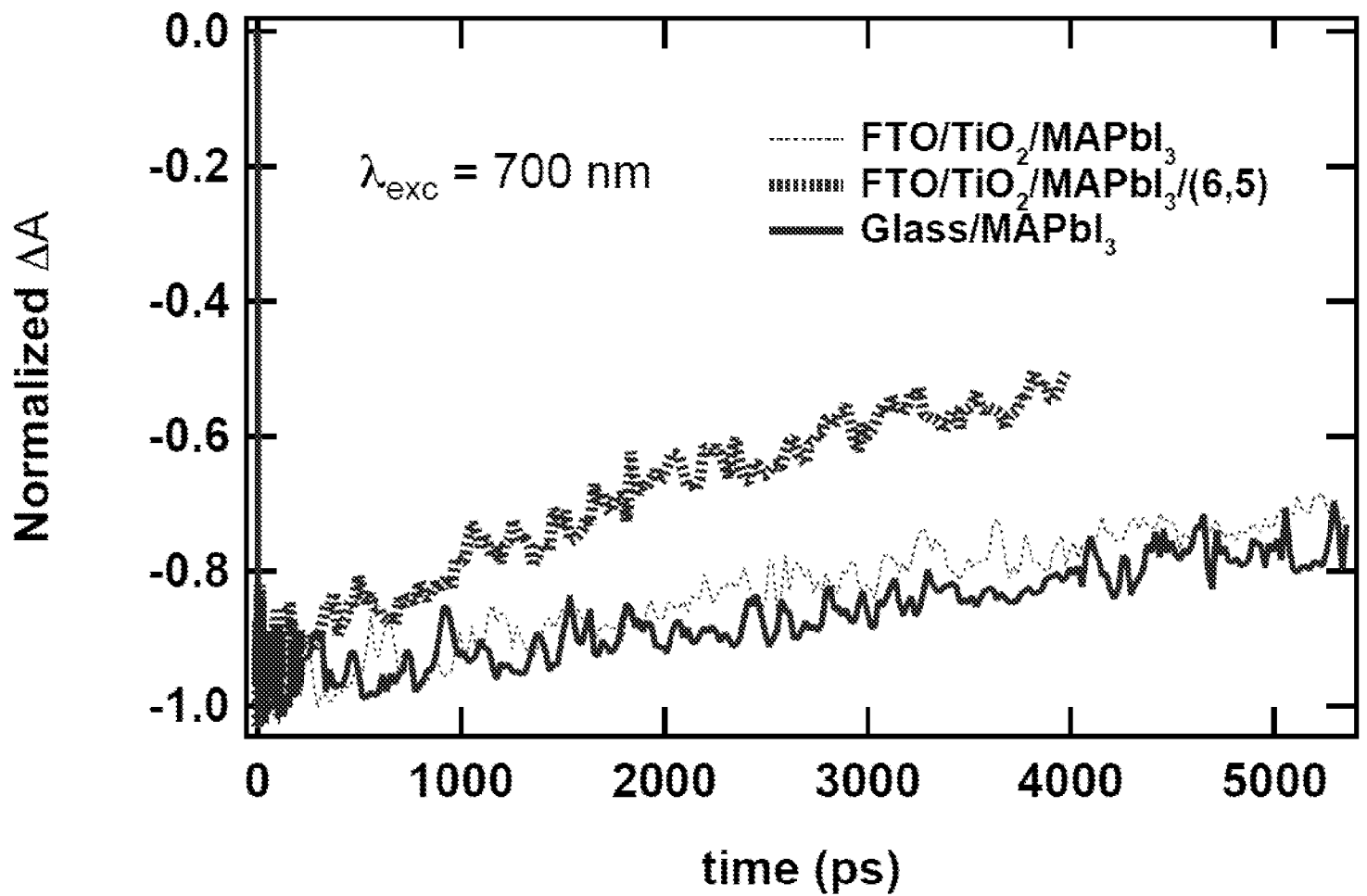


Figure 7b

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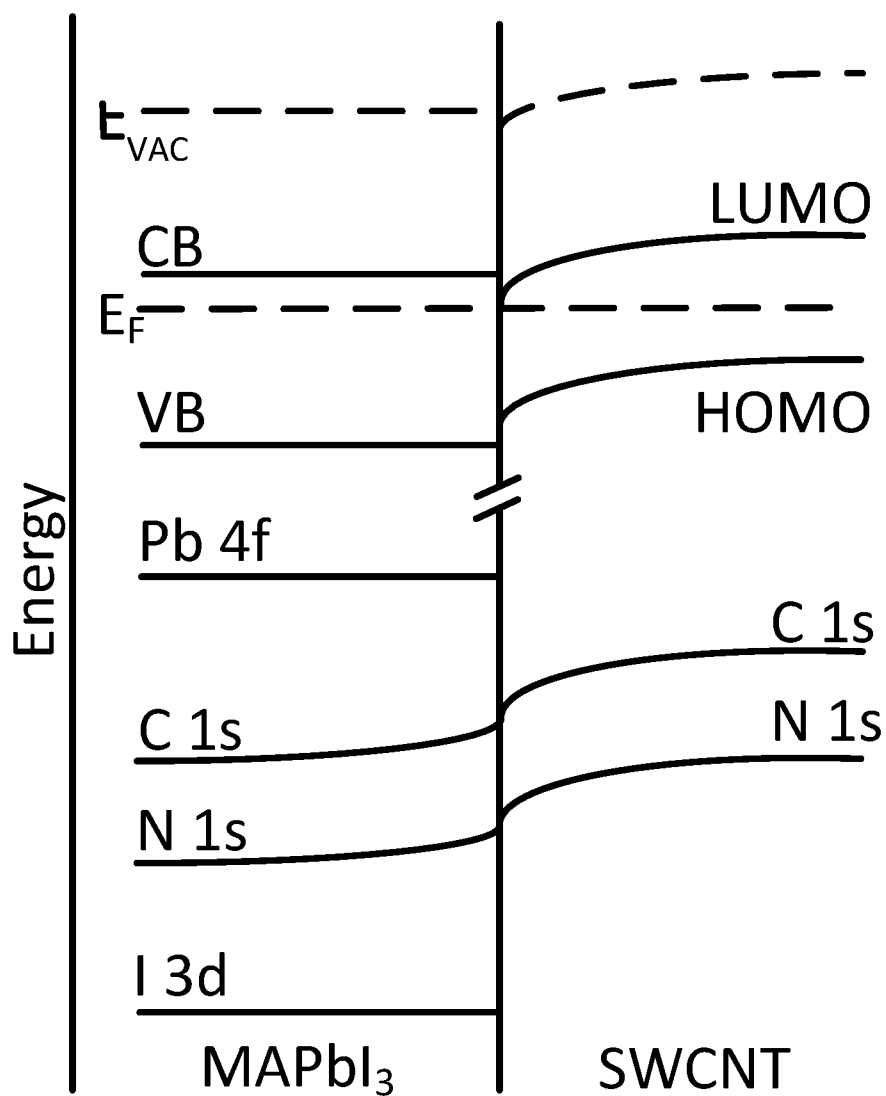


Figure 8a

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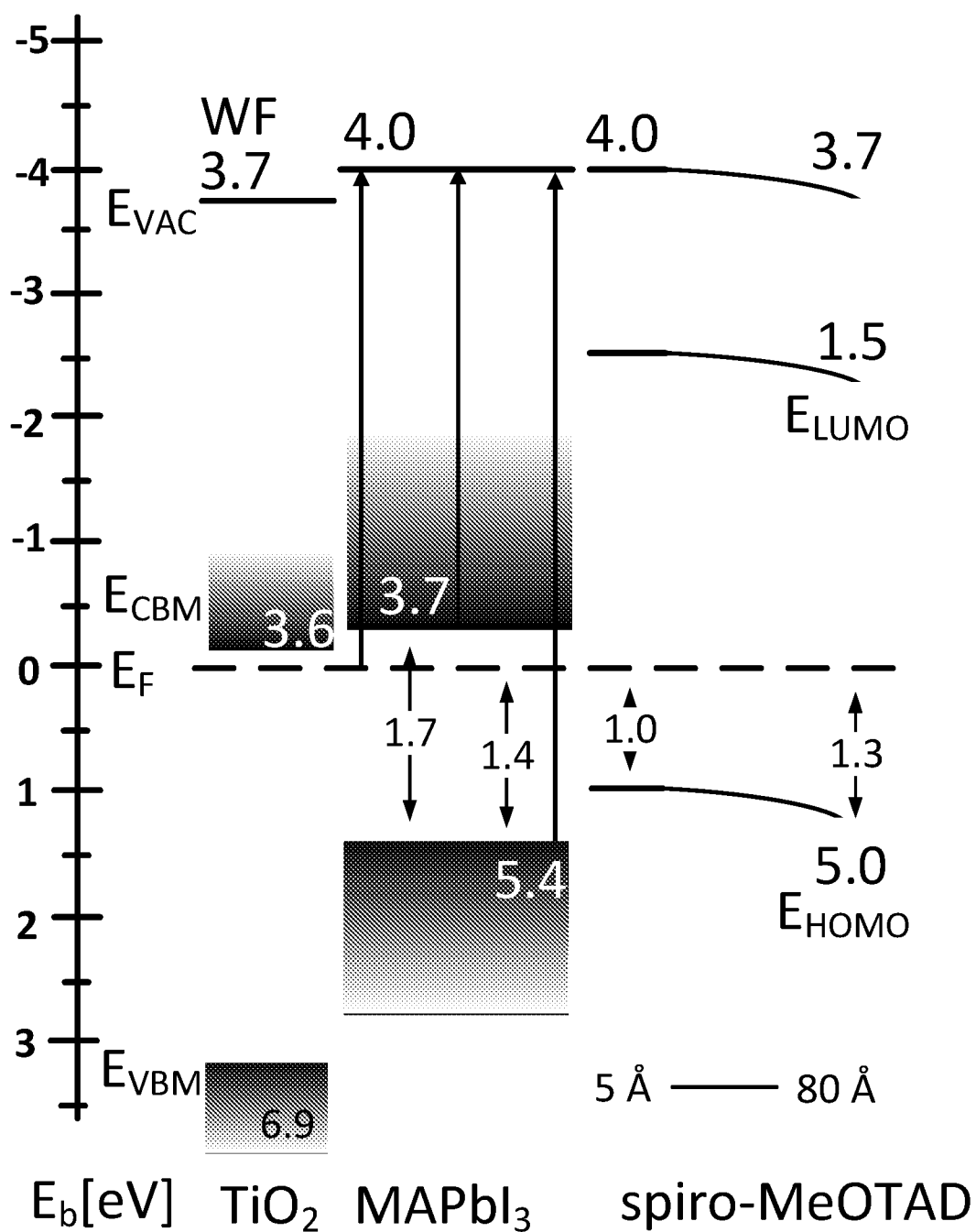


Figure 8b

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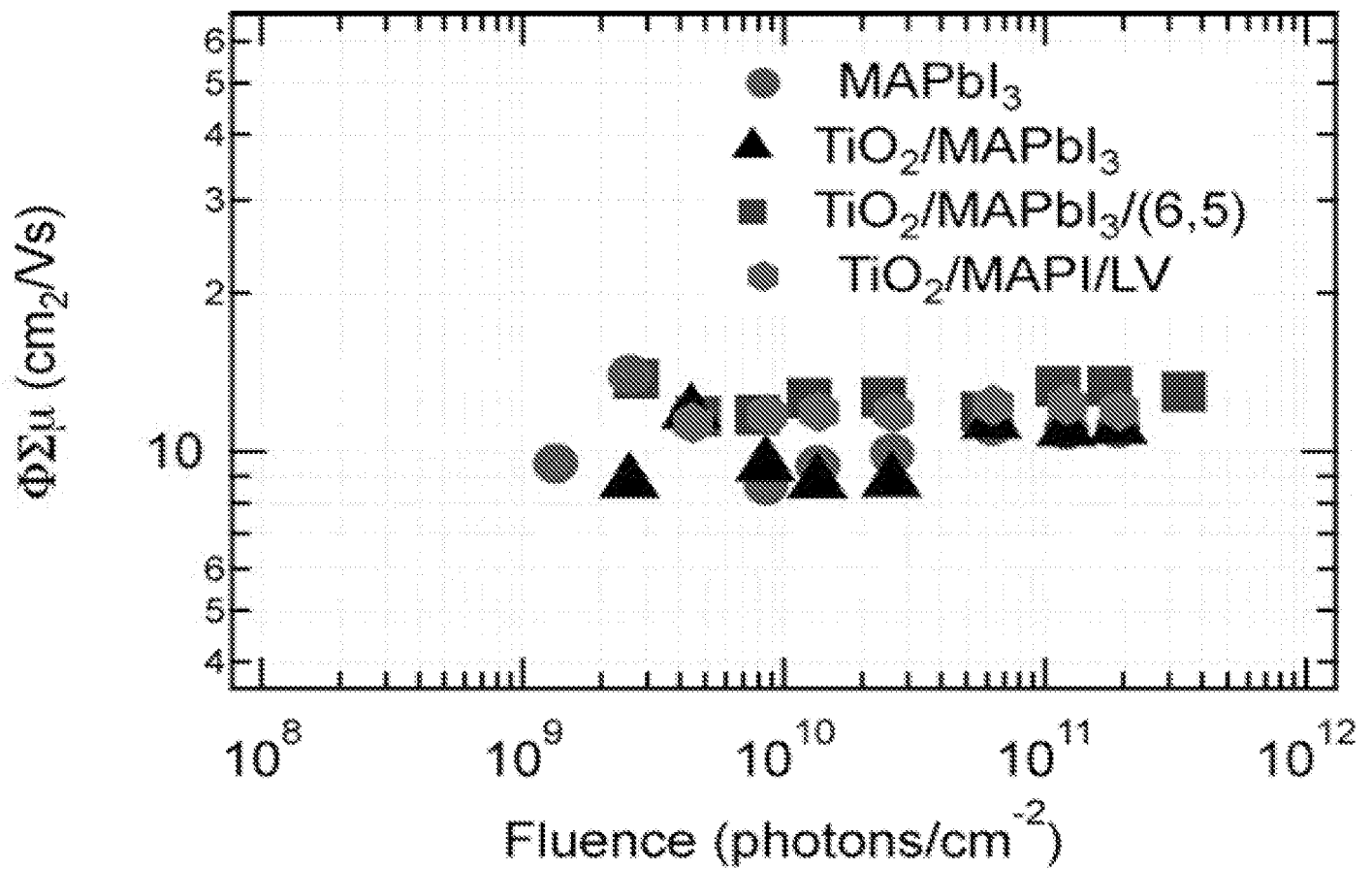


Figure 9a

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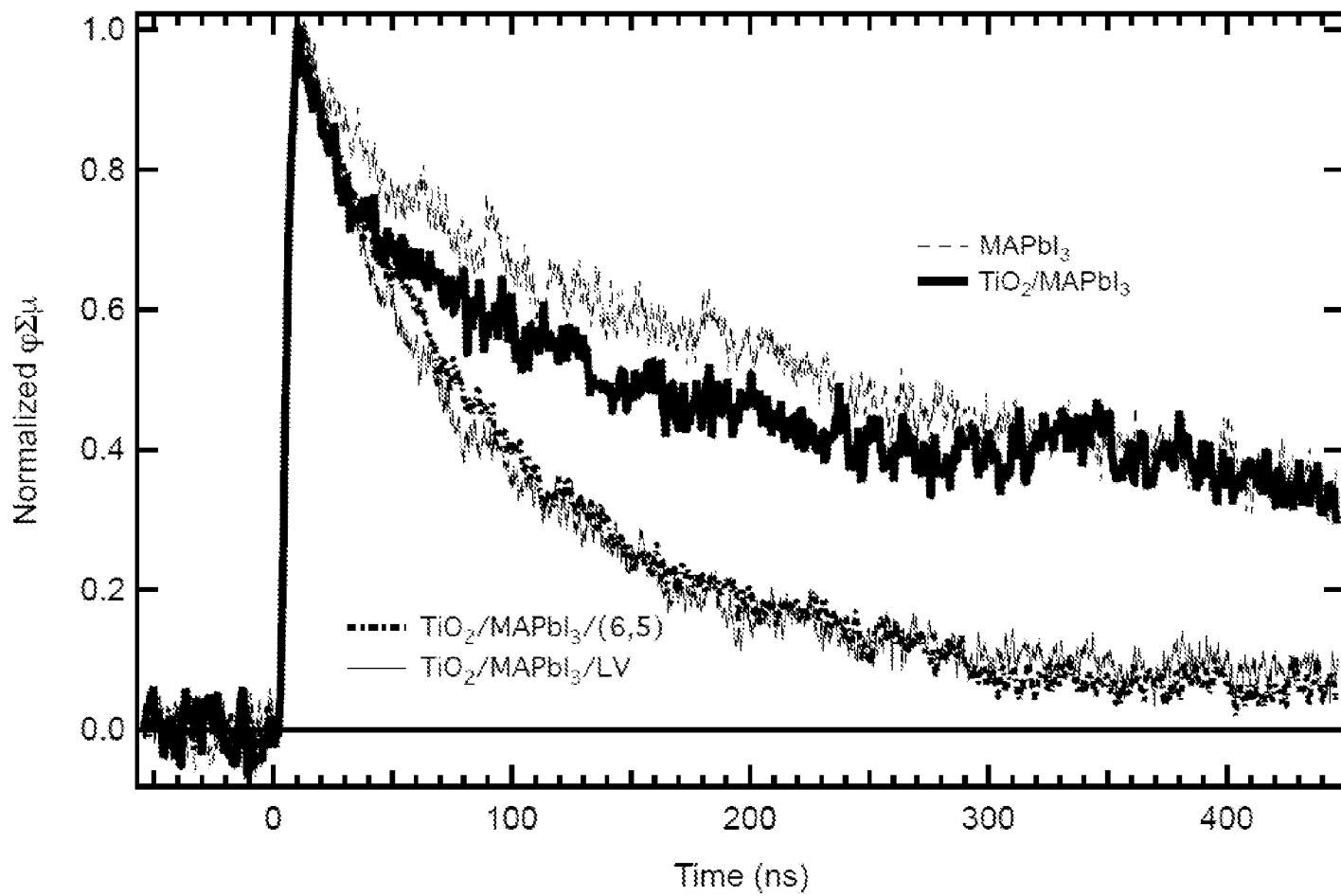


Figure 9b

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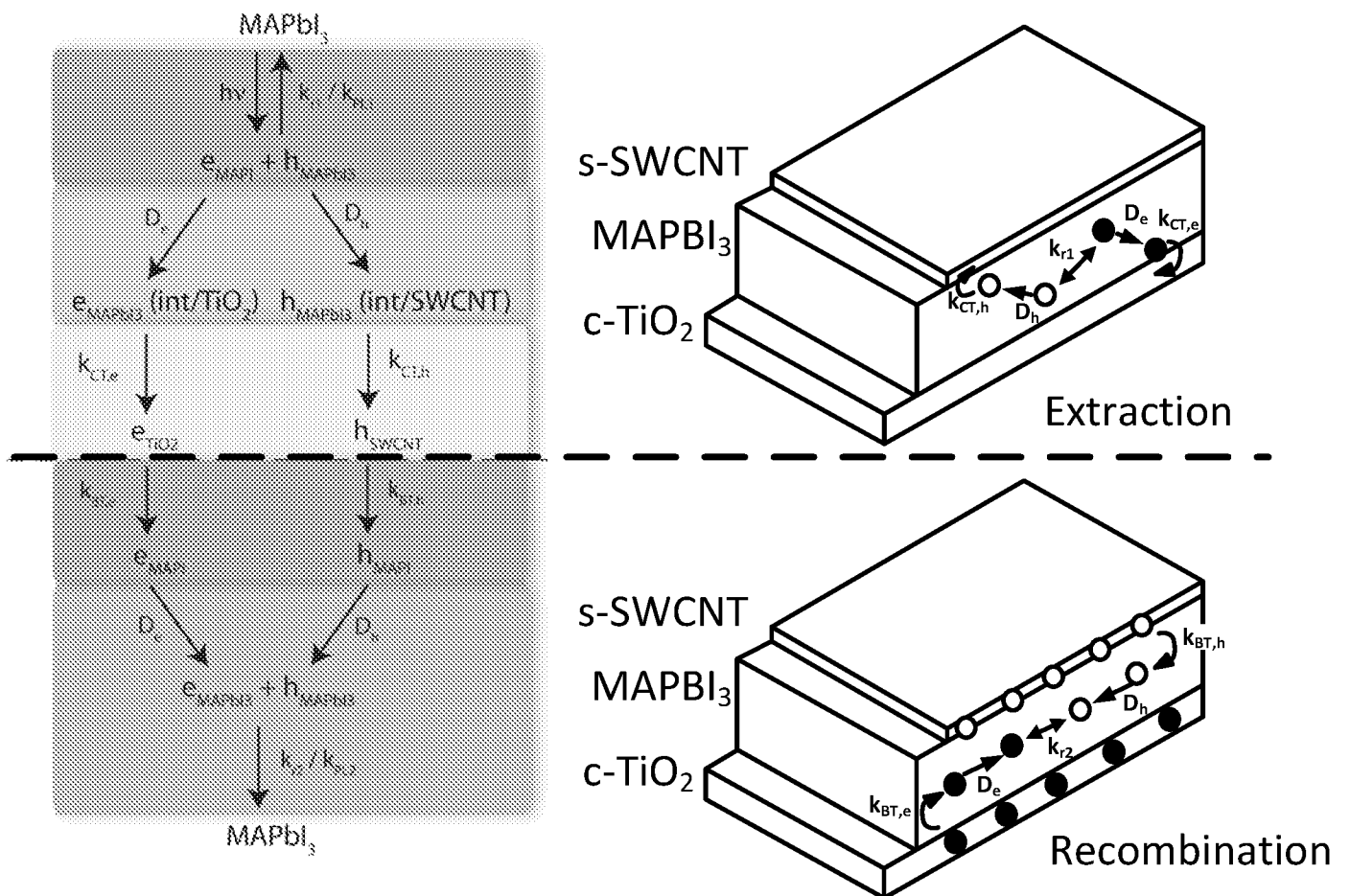


Figure 10a

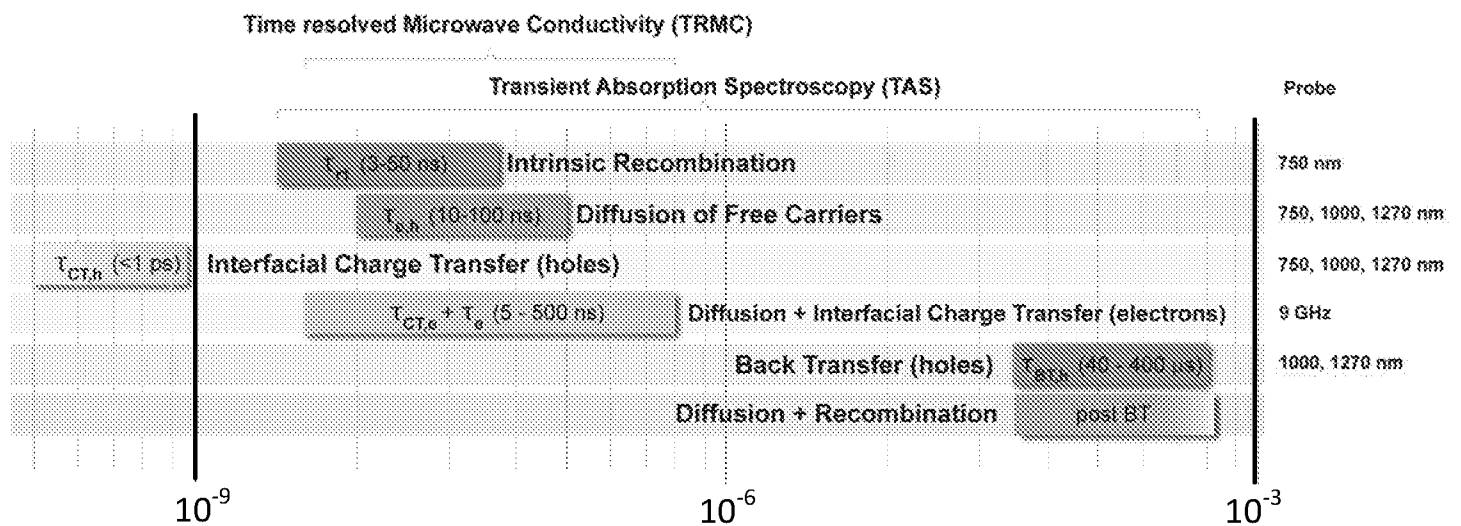


Figure 10b

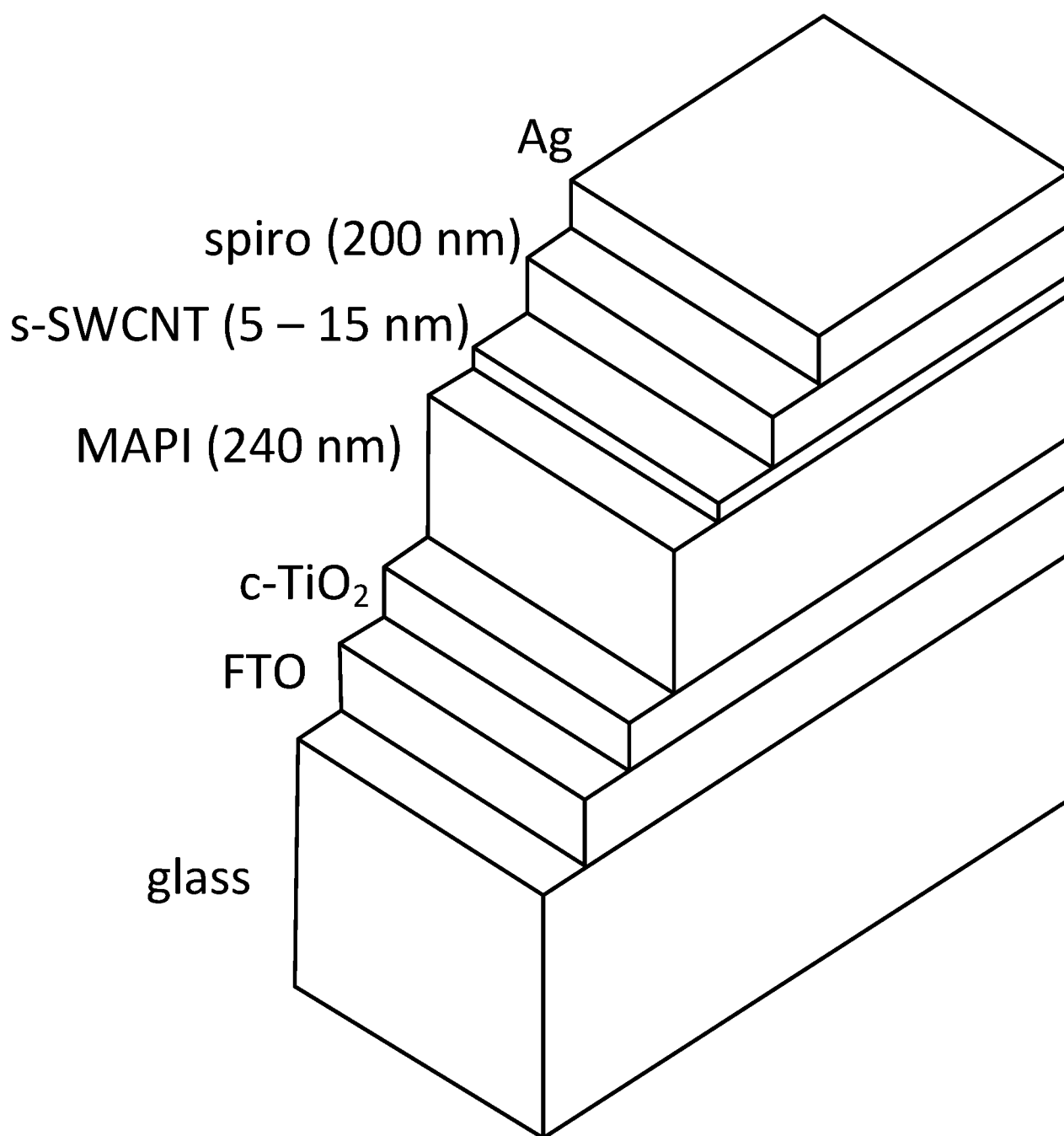


Figure 11a

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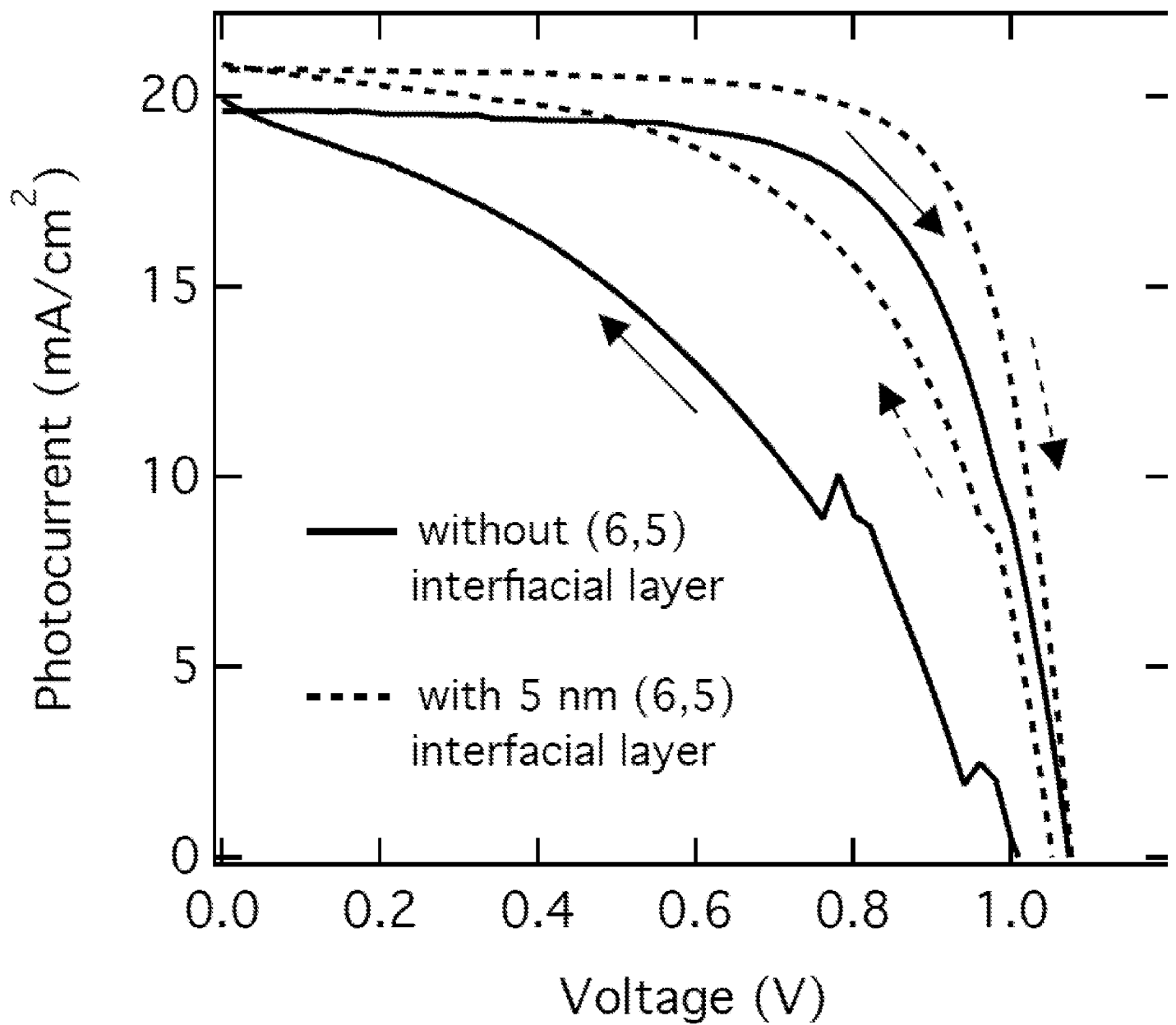


Figure 11b

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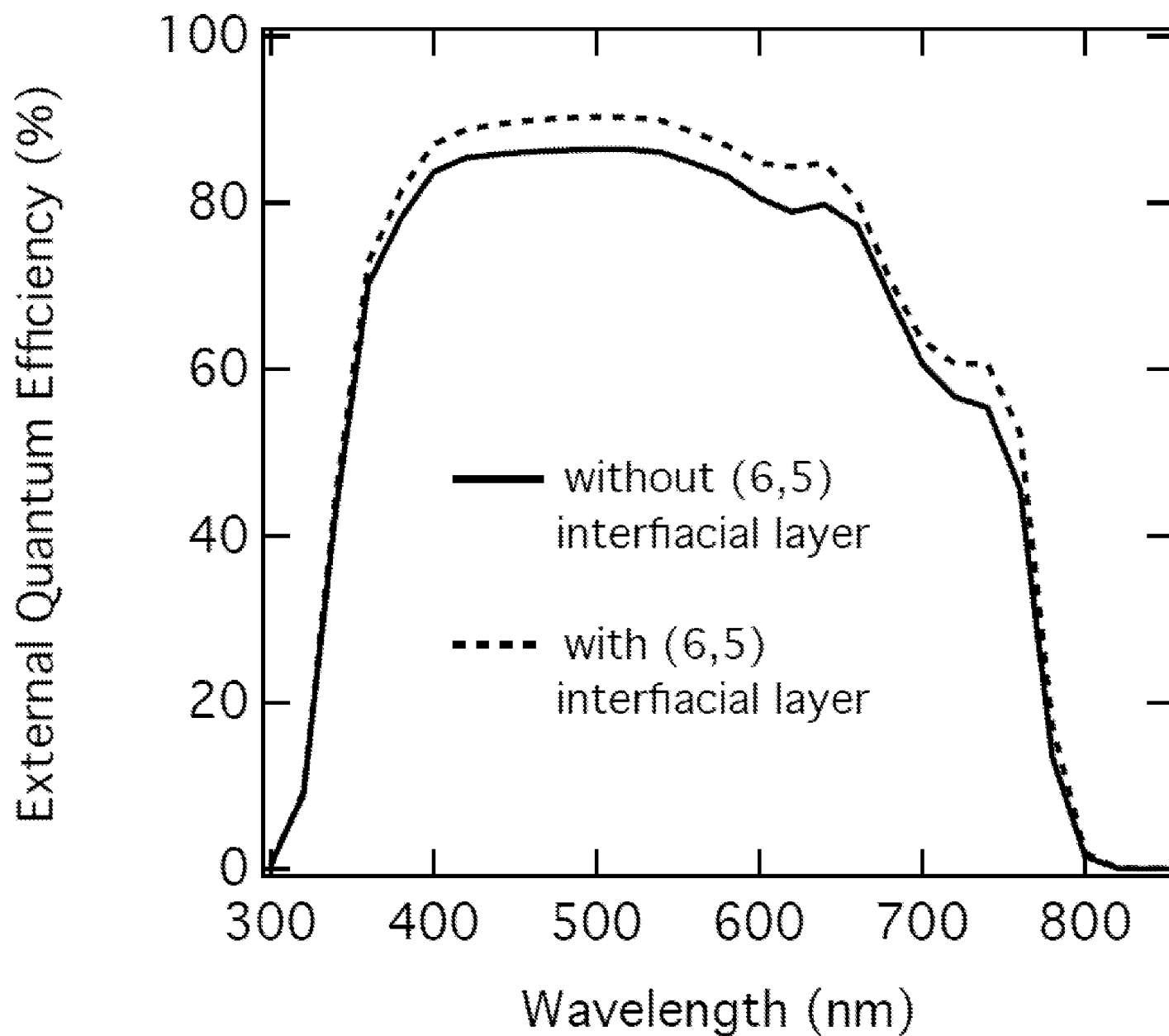


Figure 11c

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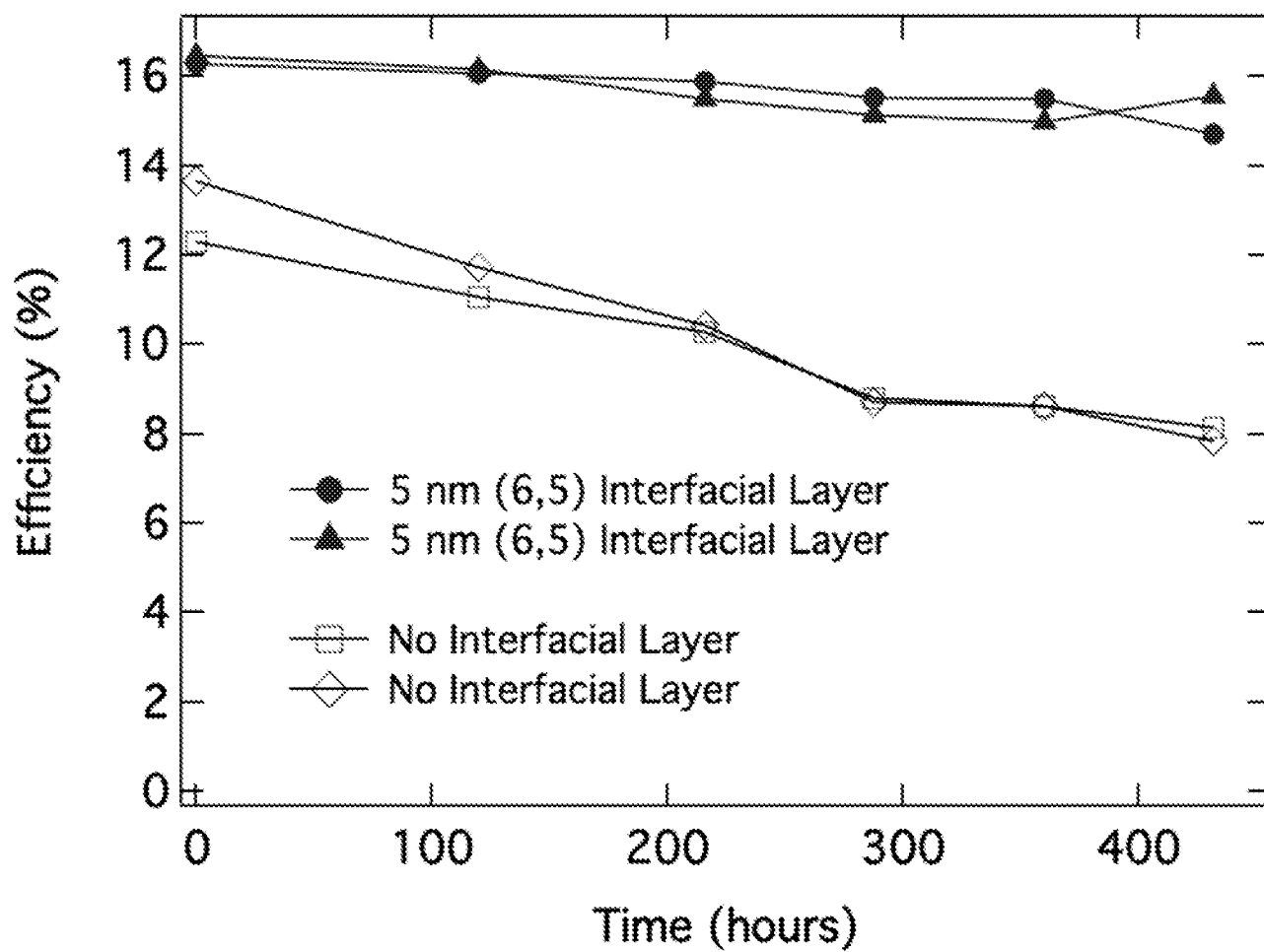


Figure 12

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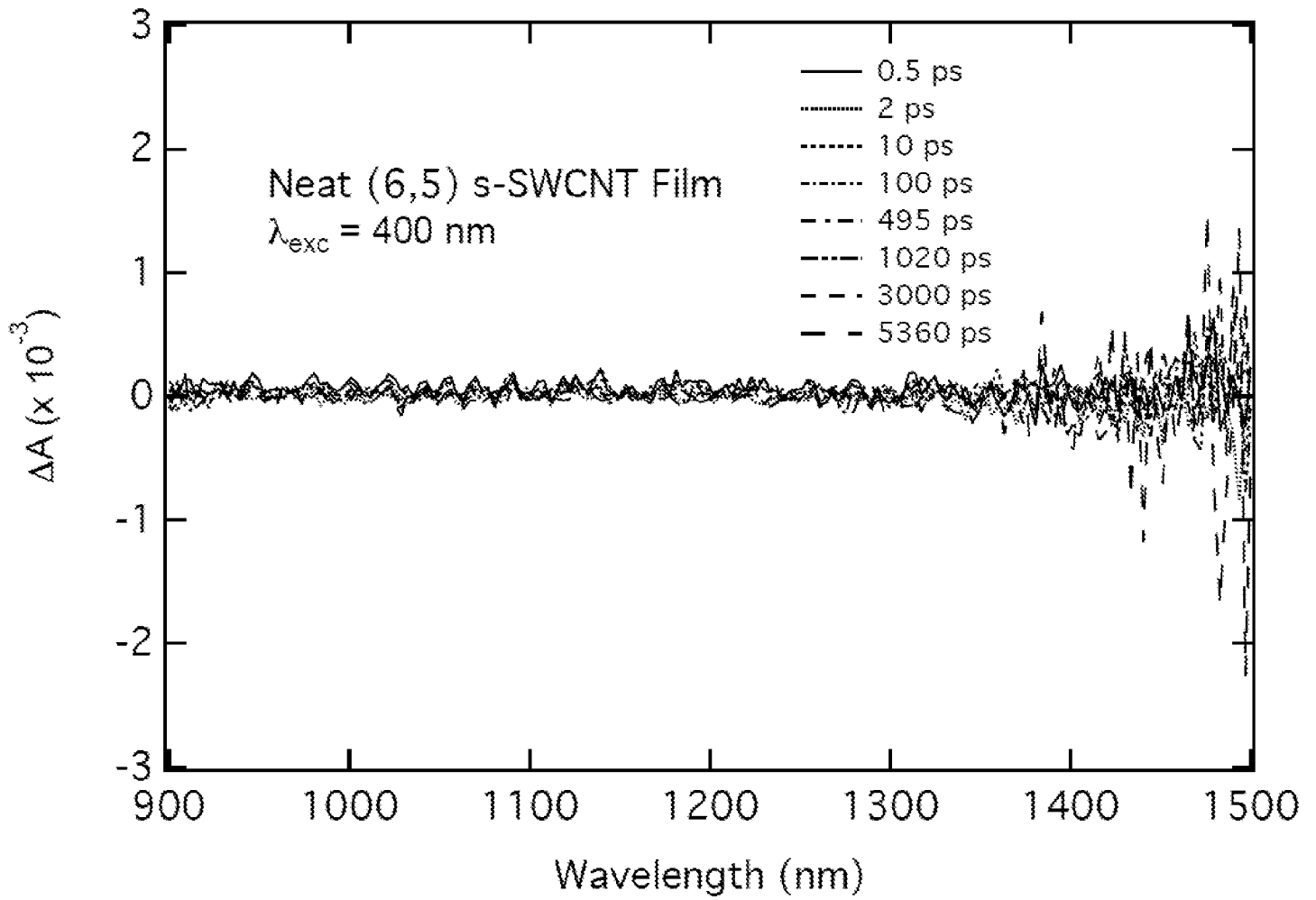


Figure 13

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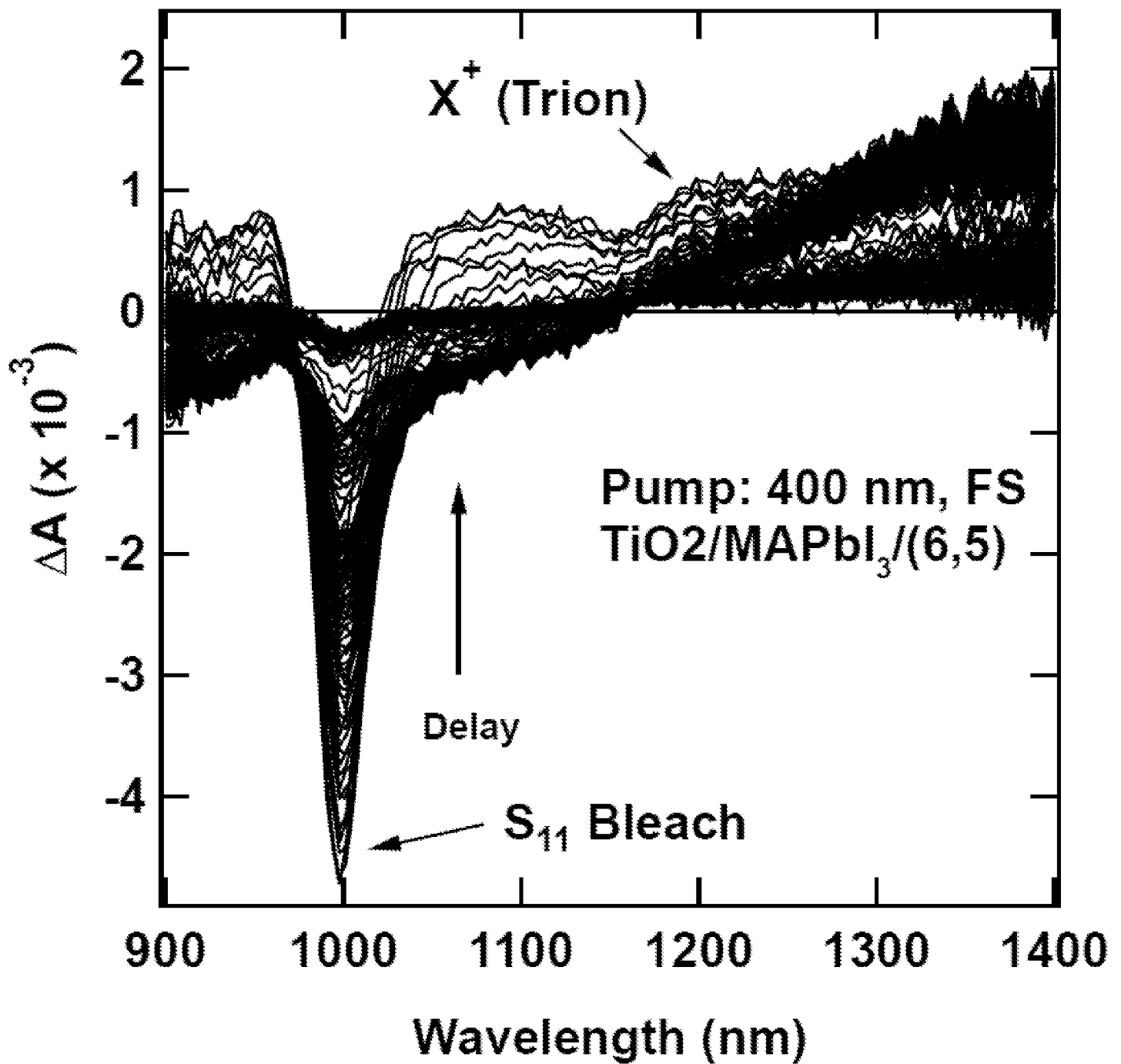


Figure 14a

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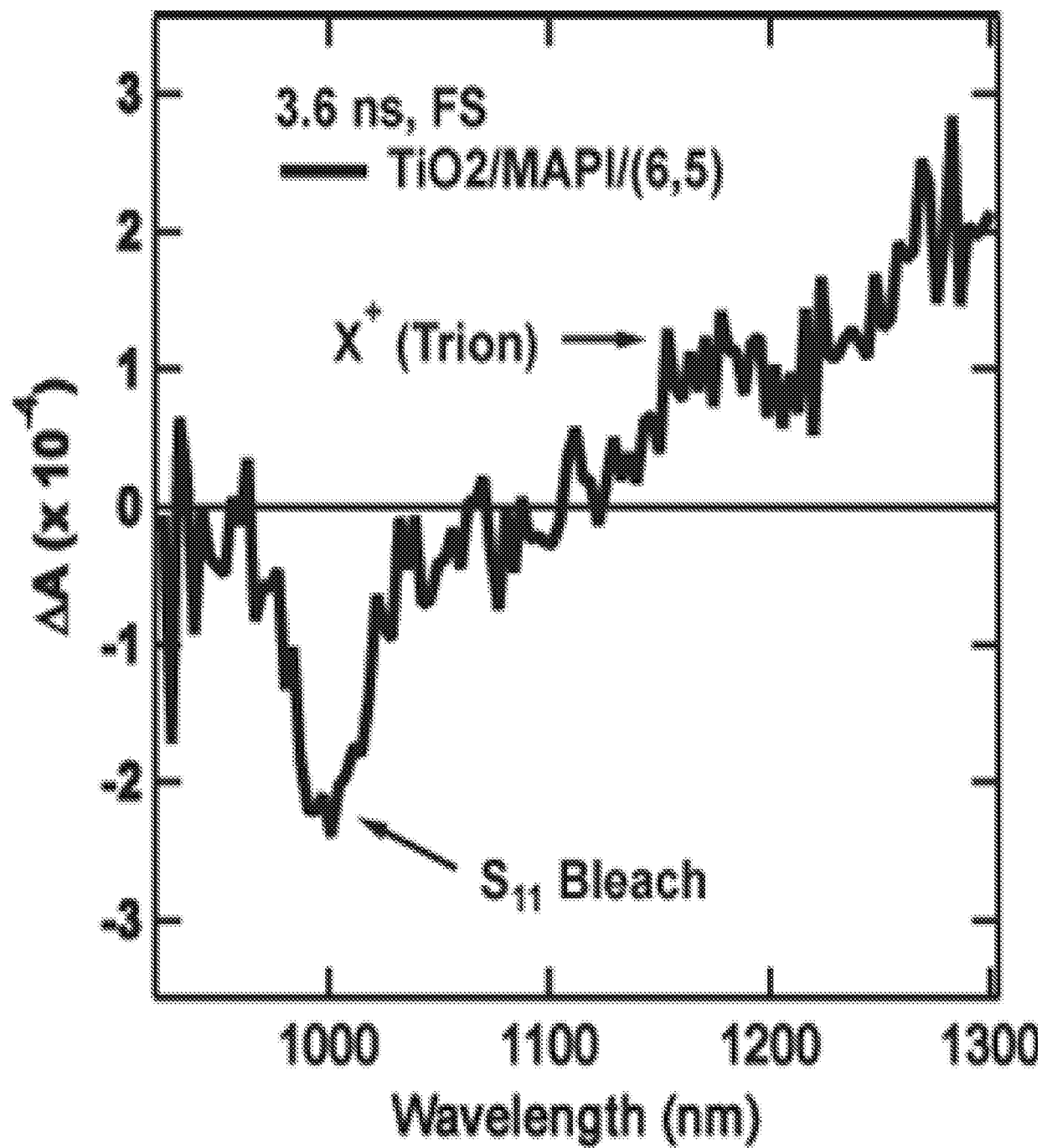


Figure 14b

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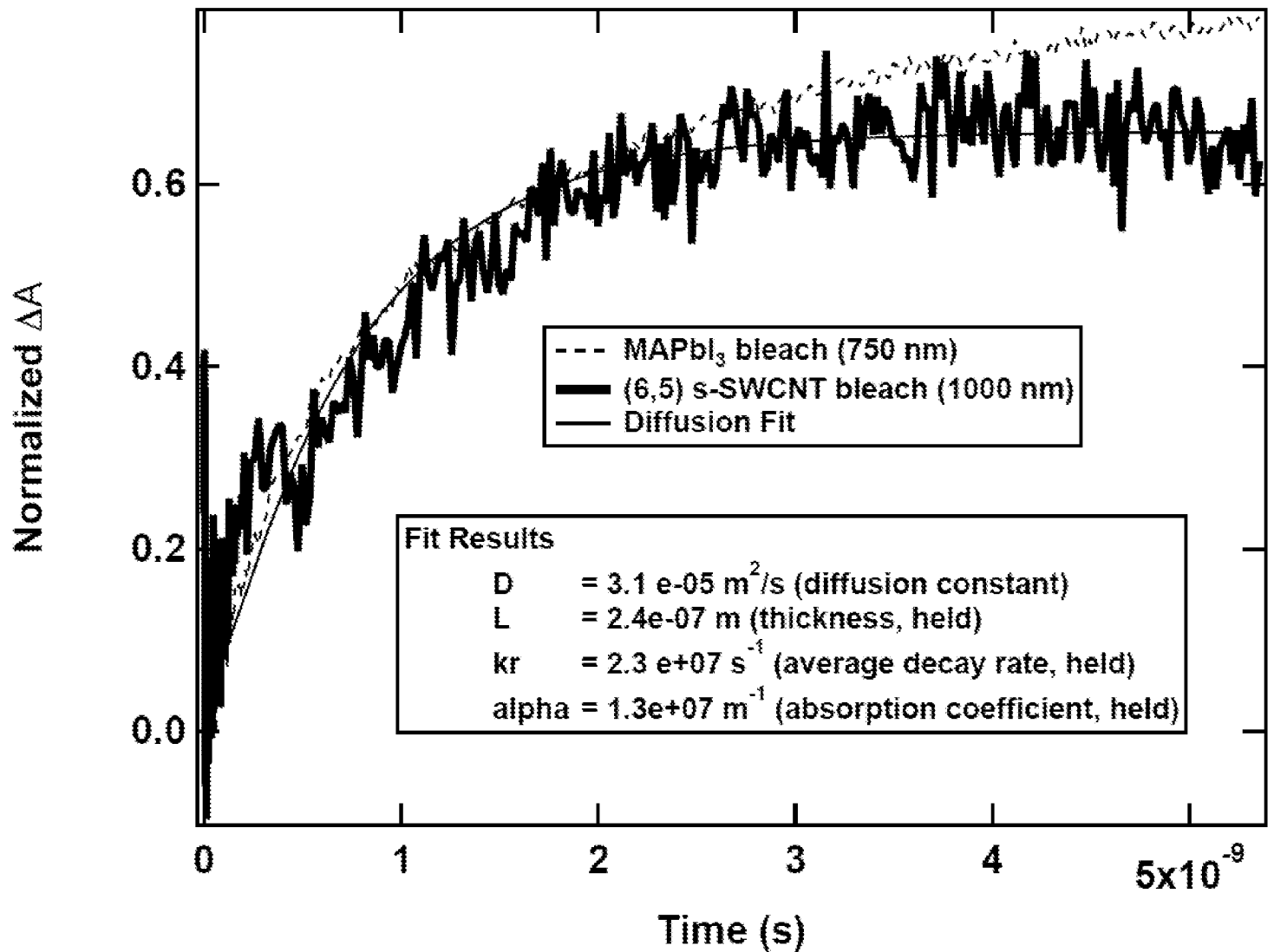


Figure 15

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US2016/064156

A. CLASSIFICATION OF SUBJECT MATTER IPC(8) - H01L 51/42; H01L 31/00; H01L 31/0248; H01L 31/0256; H01L 51/00 (2017.01) CPC - H01L 2031/0344; H01L 31/00; H01L 31/0248; H01L 31/0256; H01L 51/4213 (2017.01) According to International Patent Classification (IPC) or to both national classification and IPC		
B. FIELDS SEARCHED Minimum documentation searched (classification system followed by classification symbols) IPC(8) - H01L 31/00; H01L 31/0248; H01L 31/0256; H01L 51/00; H01L 51/42 (2017.01) CPC - H01L 31/00; H01L 31/0248; H01L 31/0256; H01L 2031/0344; H01L 51/4213 (2017.01) Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched USPC - 136/243; 136/252; 136/263; IPC(8) - H01L 31/00; H01L 31/0248; H01L 31/0256; H01L 51/00; H01L 51/42; CPC - H01L 31/00; H01L 31/0248; H01L 31/0256; H01L 2031/0344; H01L 51/4213 (keyword delimited) Electronic data base consulted during the international search (name of data base and, where practicable, search terms used) Orbit, Google Patents, Google Search terms used: alkyl, ammonium, metal, halide, chlorine, bromine, astatine, iodine, perovskite, semiconductor, layer, nanostructured; CH3NH3PbX3, CH3NH3PbI3, CH3NH3PbBr3, TiO2		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	GONZALEZ-PEDRO et al., General Working Principles of CH3NH3PbX3 Perovskite Solar Cells, Nano Letters, Vol. 14, No. 2, 12 February 2014 [retrieved on 13 January 2017]. Retrieved from the Internet: <URL: http://citeseerx.ist.psu.edu/viewdoc/download?doi=10.1.1.713.6253&rep=rep1&type=pdf >. entire document	1-3
☐ Further documents are listed in the continuation of Box C. ☐ See patent family annex.		
* Special categories of cited documents: "A" document defining the general state of the art which is not considered to be of particular relevance "E" earlier application or patent but published on or after the international filing date "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art "&" document member of the same patent family		
Date of the actual completion of the international search 13 January 2017		Date of mailing of the international search report 06 FEB 2017
Name and mailing address of the ISA/US Mail Stop PCT, Attn: ISA/US, Commissioner for Patents P.O. Box 1450, Alexandria, VA 22313-1450 Facsimile No. 571-273-8300		Authorized officer Blaine R. Copenheaver PCT Helpdesk: 571-272-4300 PCT OSP: 571-272-7774

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US2016/064156

Box No. II Observations where certain claims were found unsearchable (Continuation of item 2 of first sheet)

This international search report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:

1. ☐ Claims Nos.:
because they relate to subject matter not required to be searched by this Authority, namely:
2. ☐ Claims Nos.:
because they relate to parts of the international application that do not comply with the prescribed requirements to such an extent that no meaningful international search can be carried out, specifically:
3. ☒ Claims Nos.: 4-18
because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).

Box No. III Observations where unity of invention is lacking (Continuation of item 3 of first sheet)

This International Searching Authority found multiple inventions in this international application, as follows:

1. ☐ As all required additional search fees were timely paid by the applicant, this international search report covers all searchable claims.
2. ☐ As all searchable claims could be searched without effort justifying additional fees, this Authority did not invite payment of additional fees.
3. ☐ As only some of the required additional search fees were timely paid by the applicant, this international search report covers only those claims for which fees were paid, specifically claims Nos.:
4. ☐ No required additional search fees were timely paid by the applicant. Consequently, this international search report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.:

Remark on Protest

- ☐ The additional search fees were accompanied by the applicant's protest and, where applicable, the payment of a protest fee.
- ☐ The additional search fees were accompanied by the applicant's protest but the applicable protest fee was not paid within the time limit specified in the invitation.
- ☐ No protest accompanied the payment of additional search fees.